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(54) **SEMICONDUCTOR PACKAGE AND METHOD OF FABRICATING THE SAME**

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(57) **ABSTRACT**

Semiconductor packages and their fabrication methods are provided. A semiconductor package includes a first redistribution layer, a first semiconductor chip on the first redistribution layer, a first adhesive layer on the first semiconductor chip, a first molding layer on the first redistribution layer, a second semiconductor chip on the first adhesive layer, a second adhesive layer on the second semiconductor chip, a second molding layer on the first molding layer, and a second redistribution layer on the second molding layer. The first semiconductor chip includes a first connection terminal that penetrates the first adhesive layer such as to be exposed at a top surface of the first adhesive layer. The second semiconductor chip includes a second connection terminal that penetrates the second molding layer such as to be coupled to the first connection terminal.

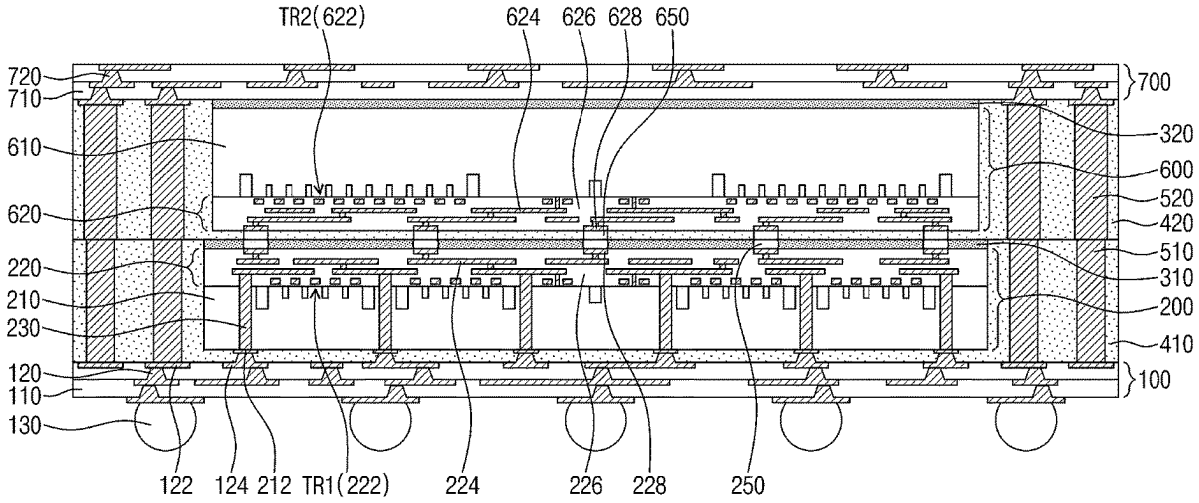

FIG. 1

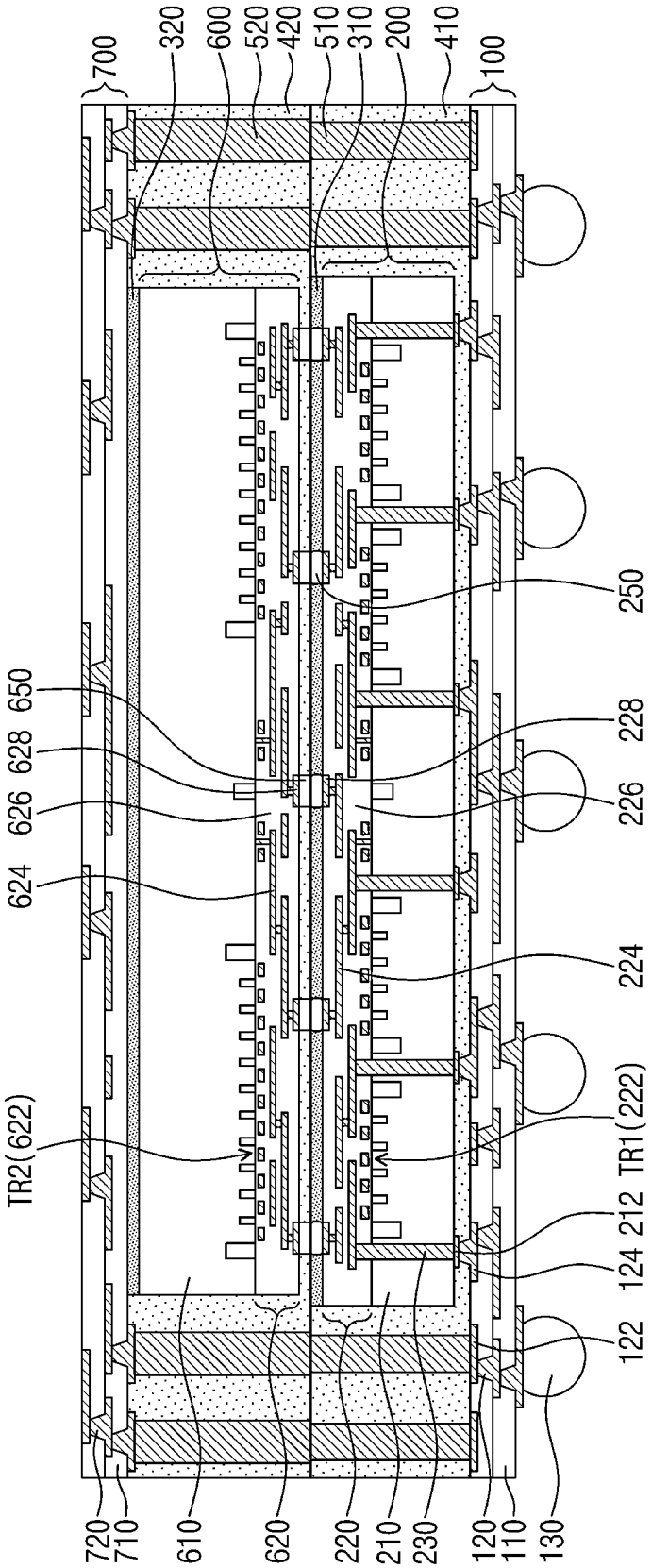
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FIG. 2

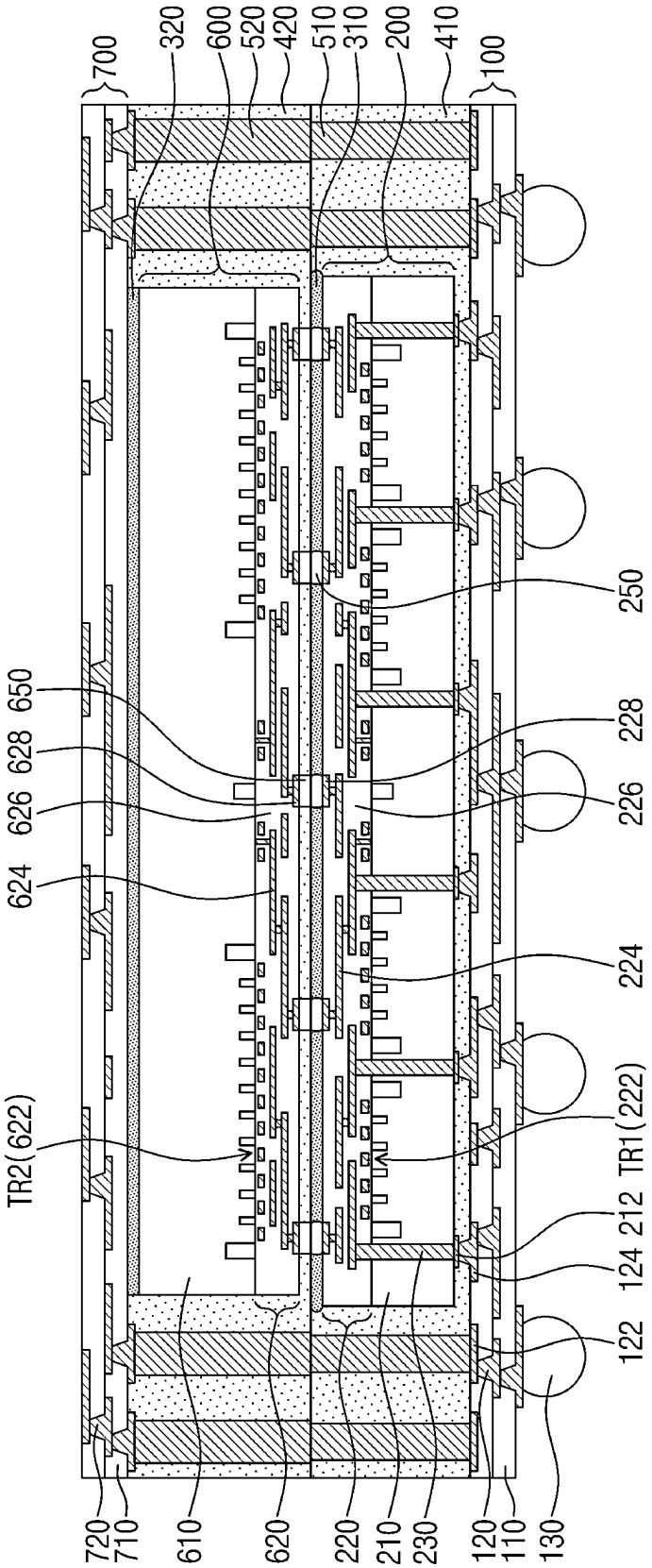
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FIG. 3

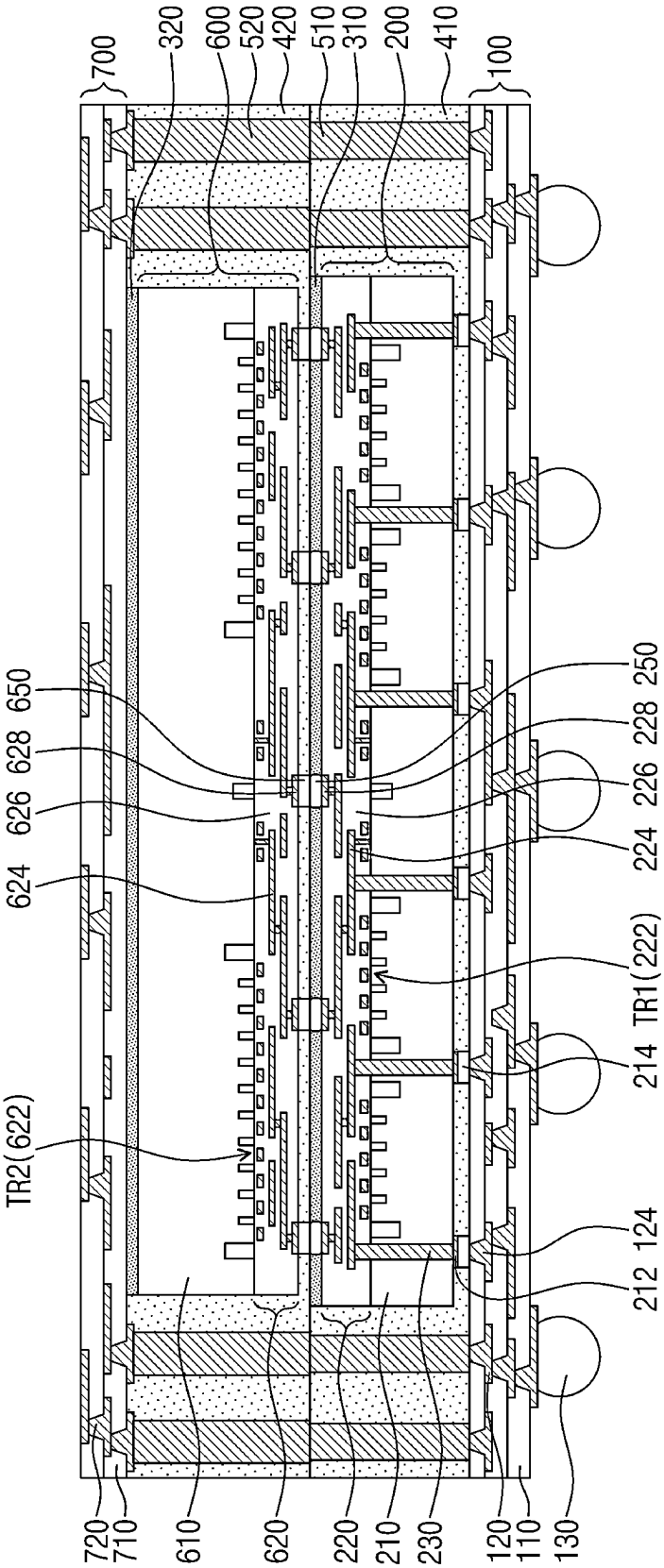
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FIG. 4

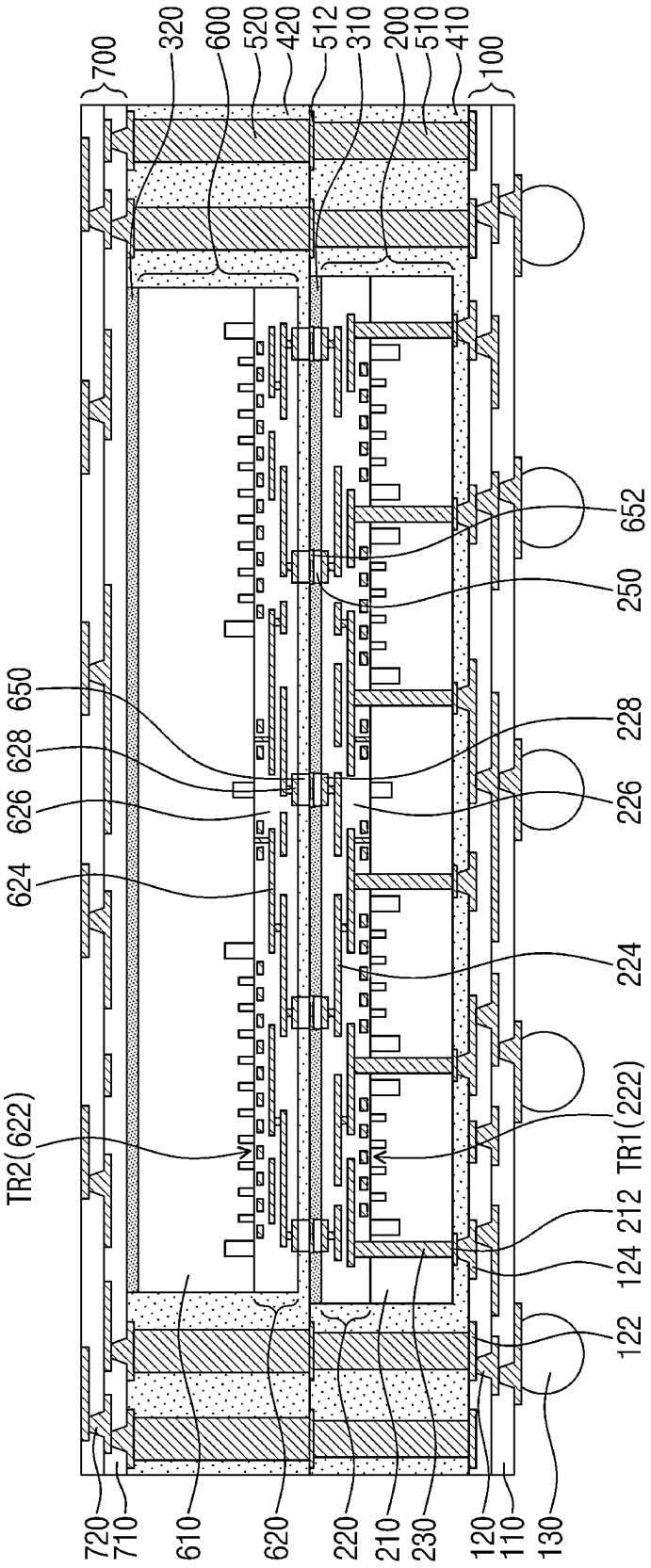
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FIG. 5

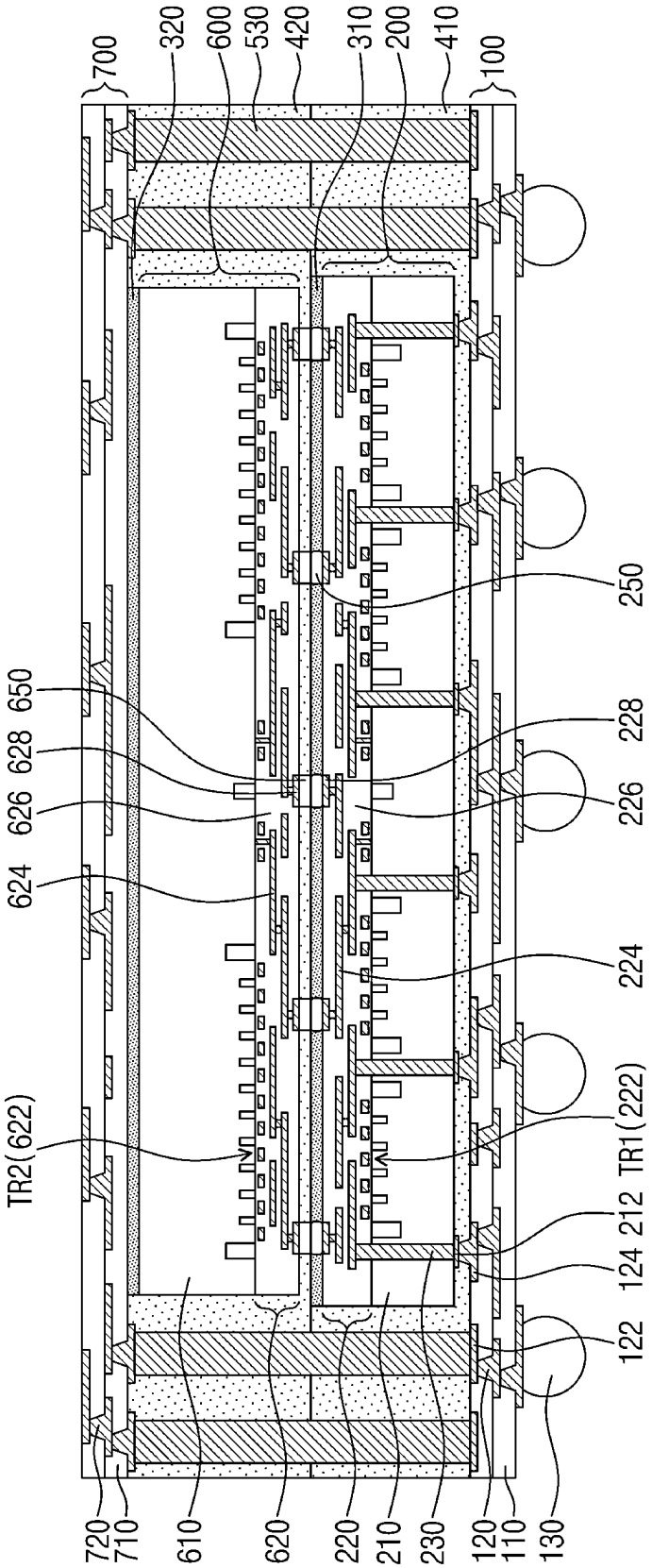
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FIG. 6

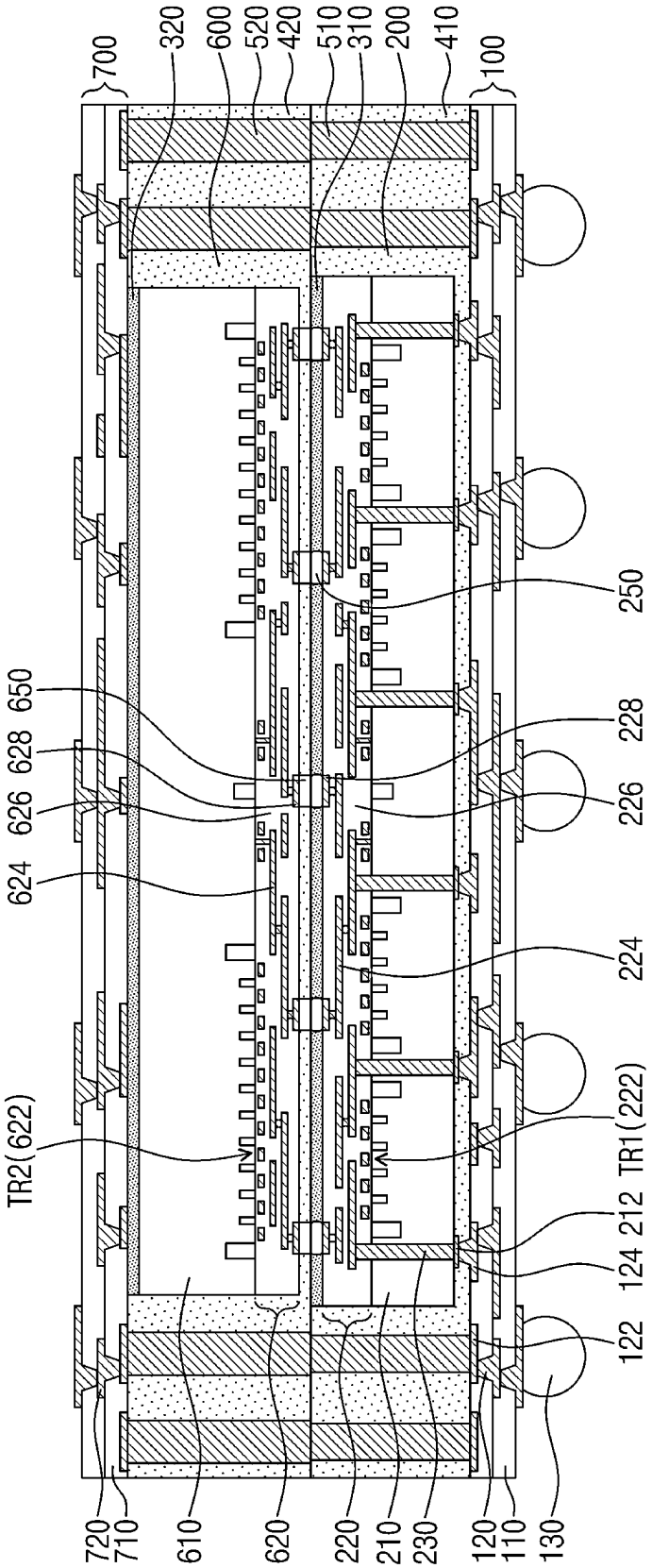
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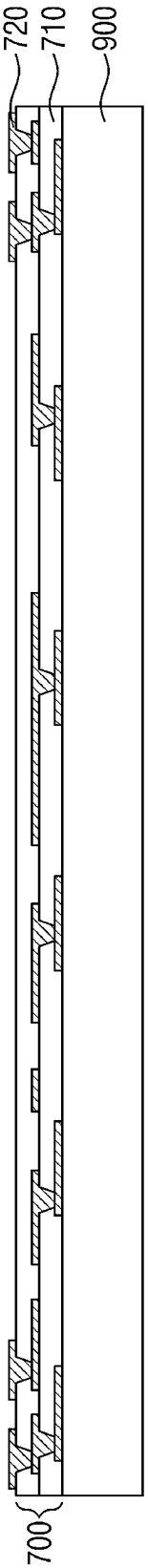
FIG. 7



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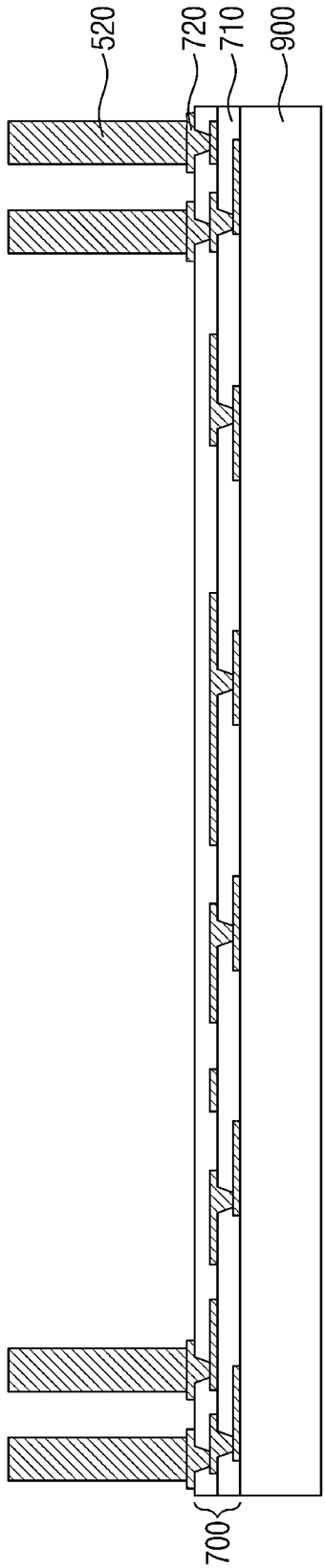

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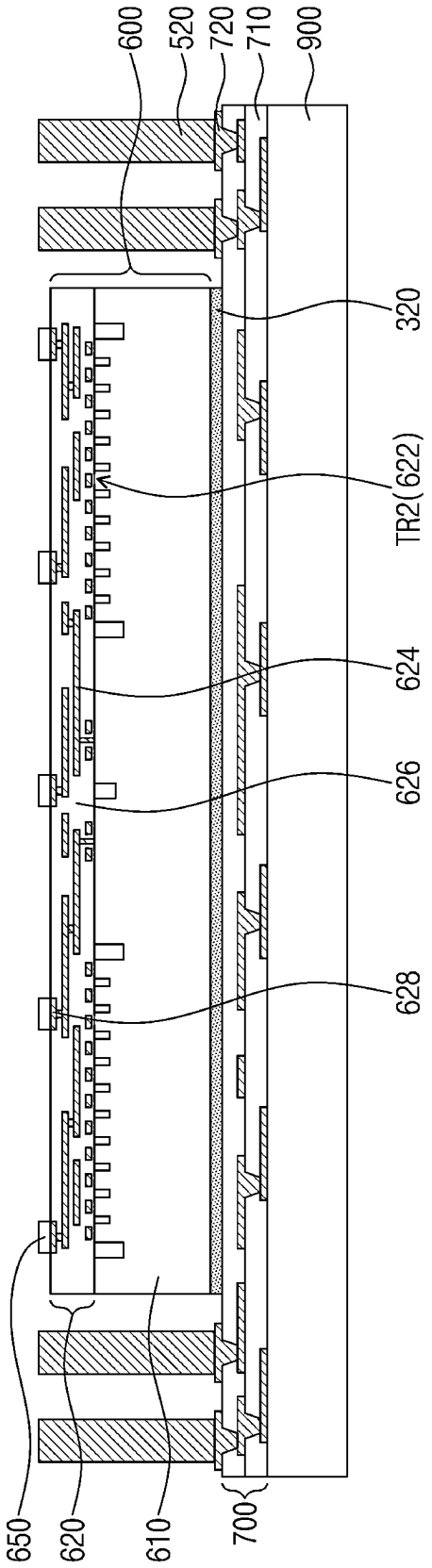

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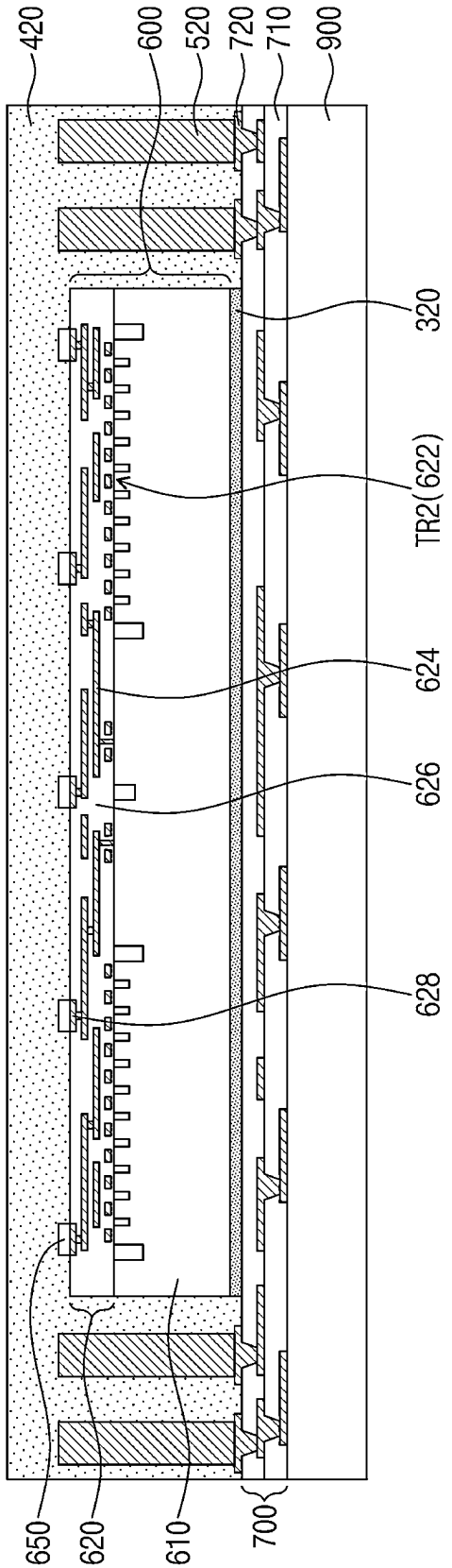

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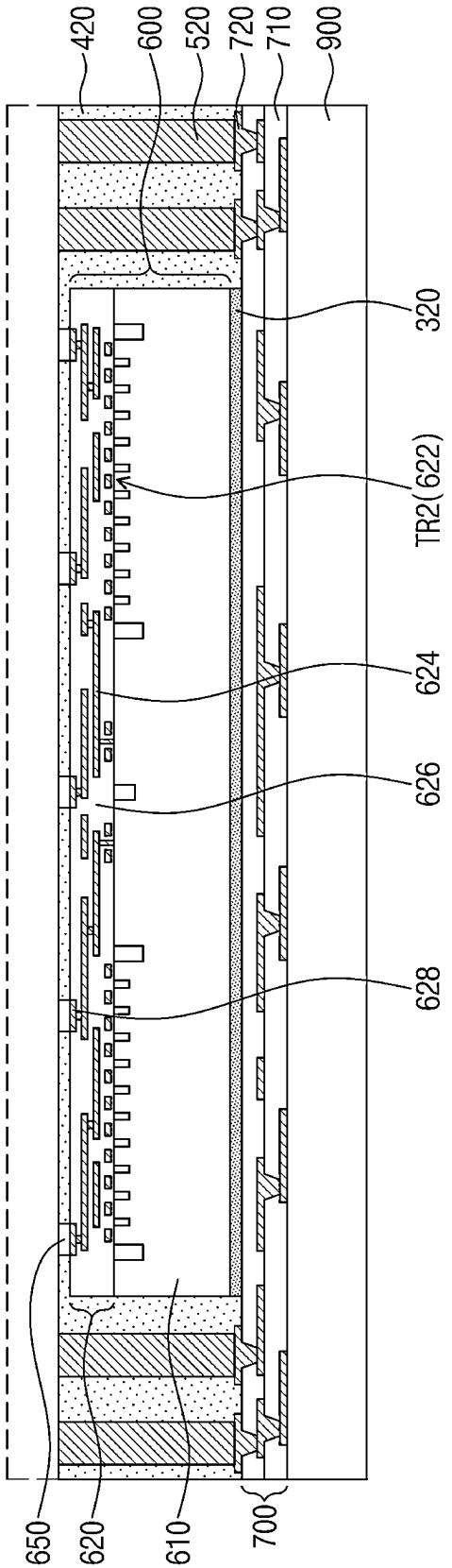

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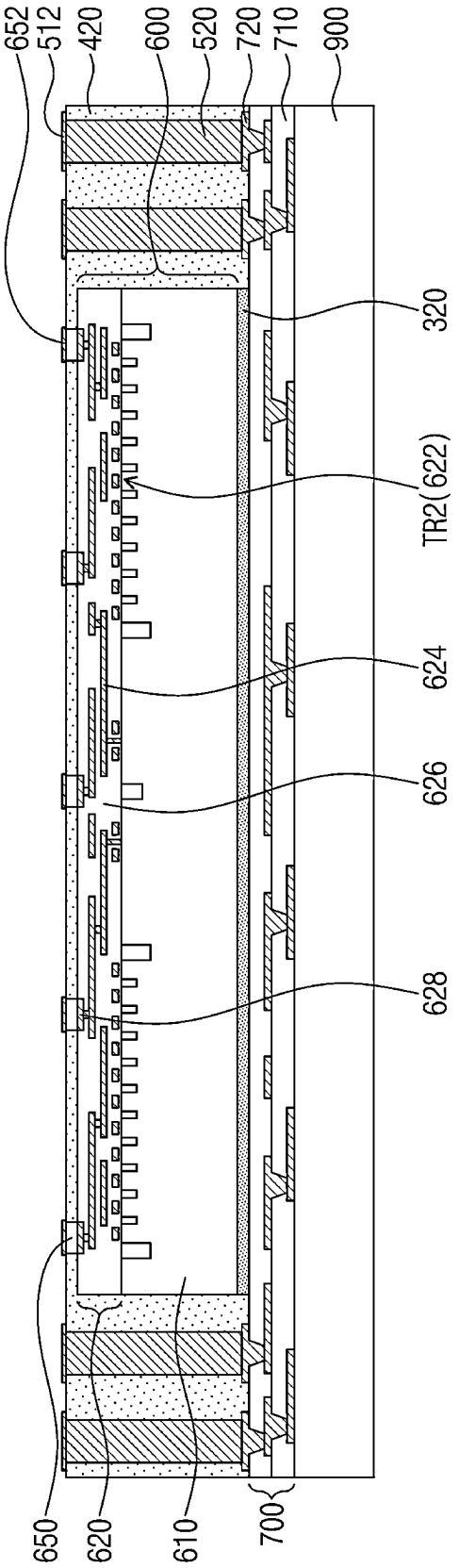
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FIG. 13

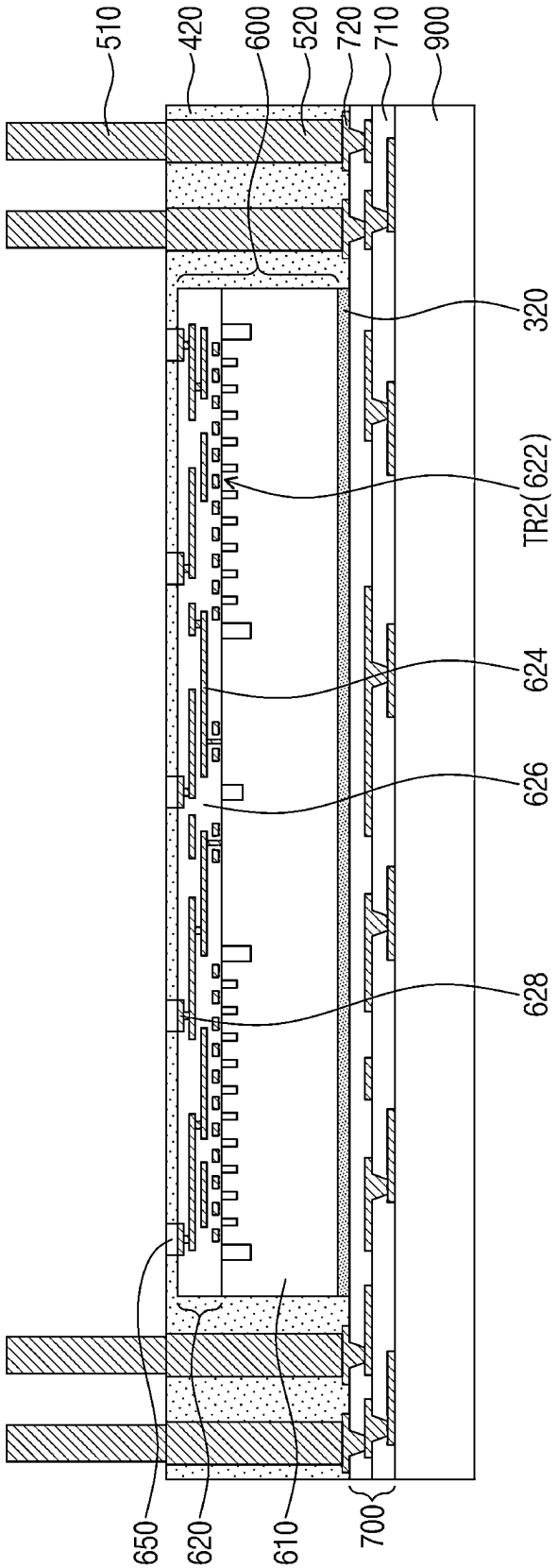
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FIG. 14

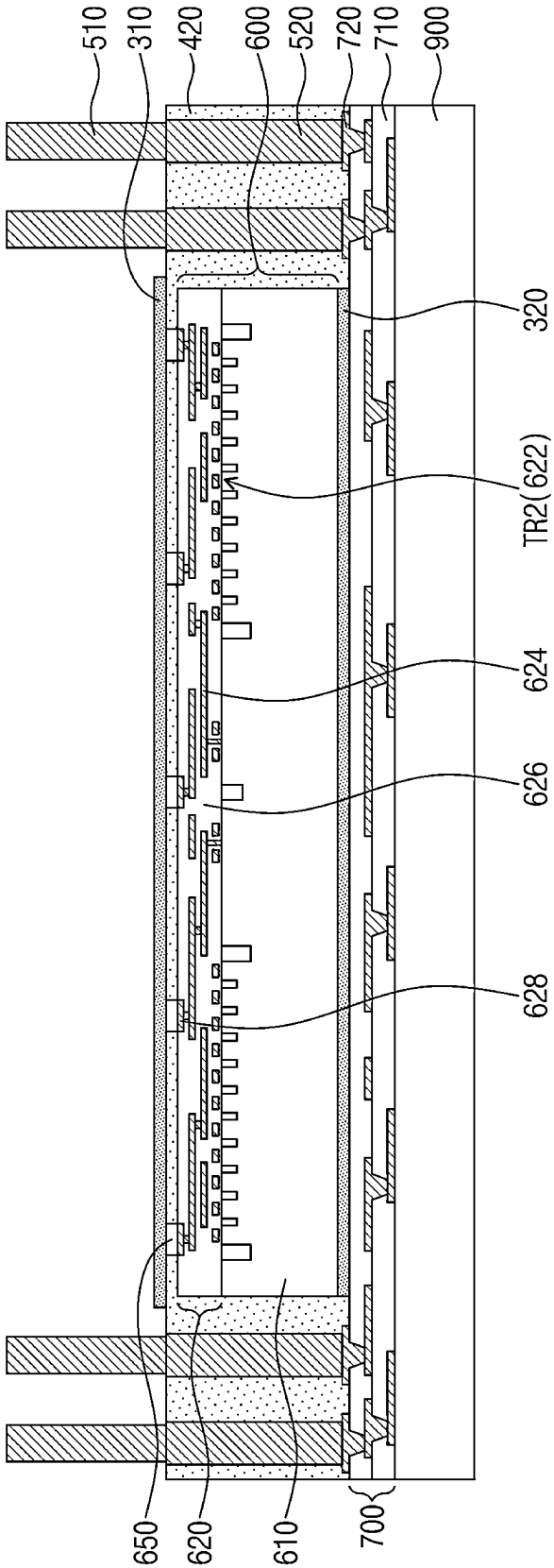
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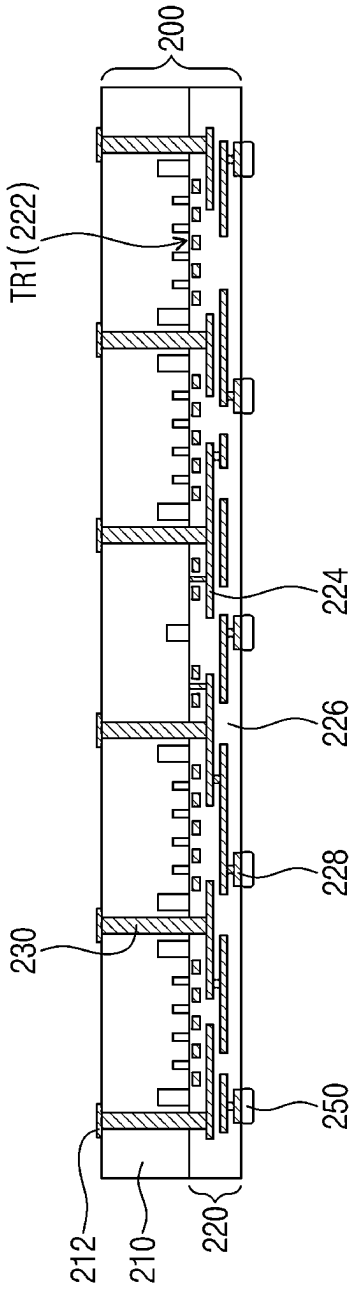
FIG. 15



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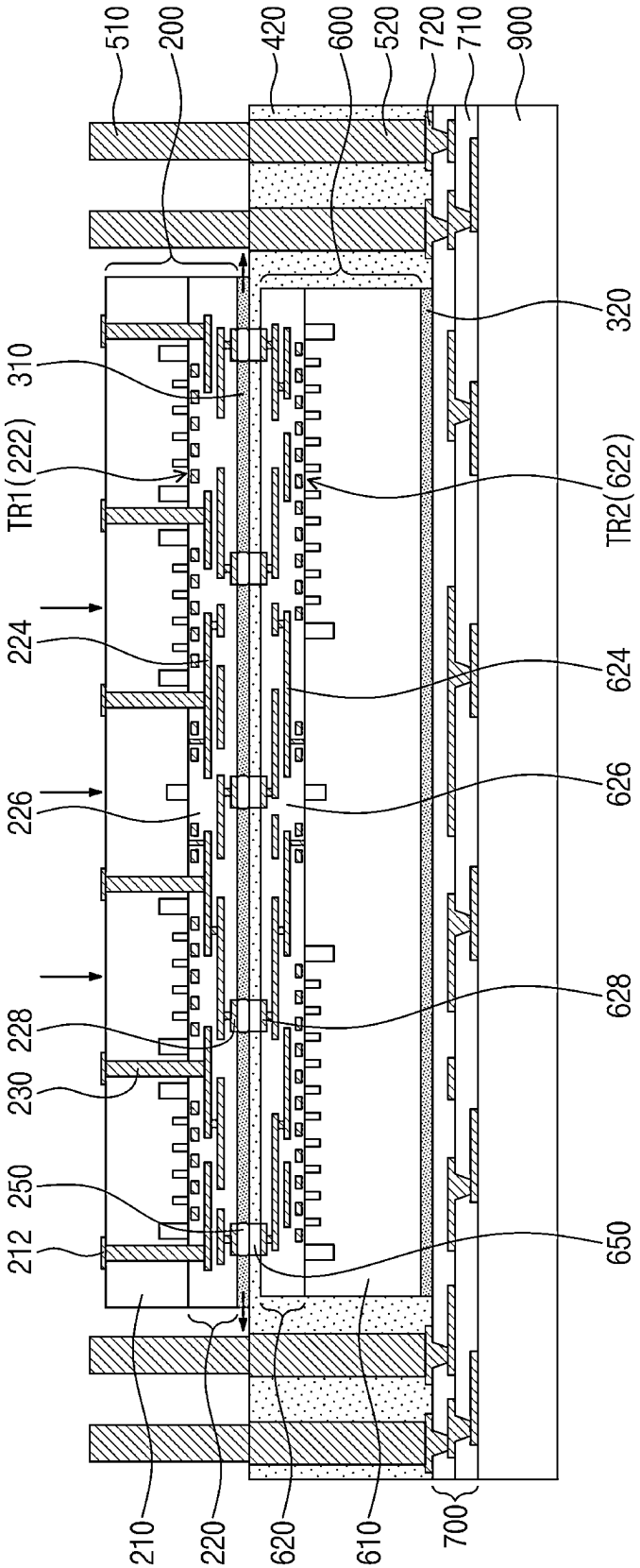
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FIG. 17

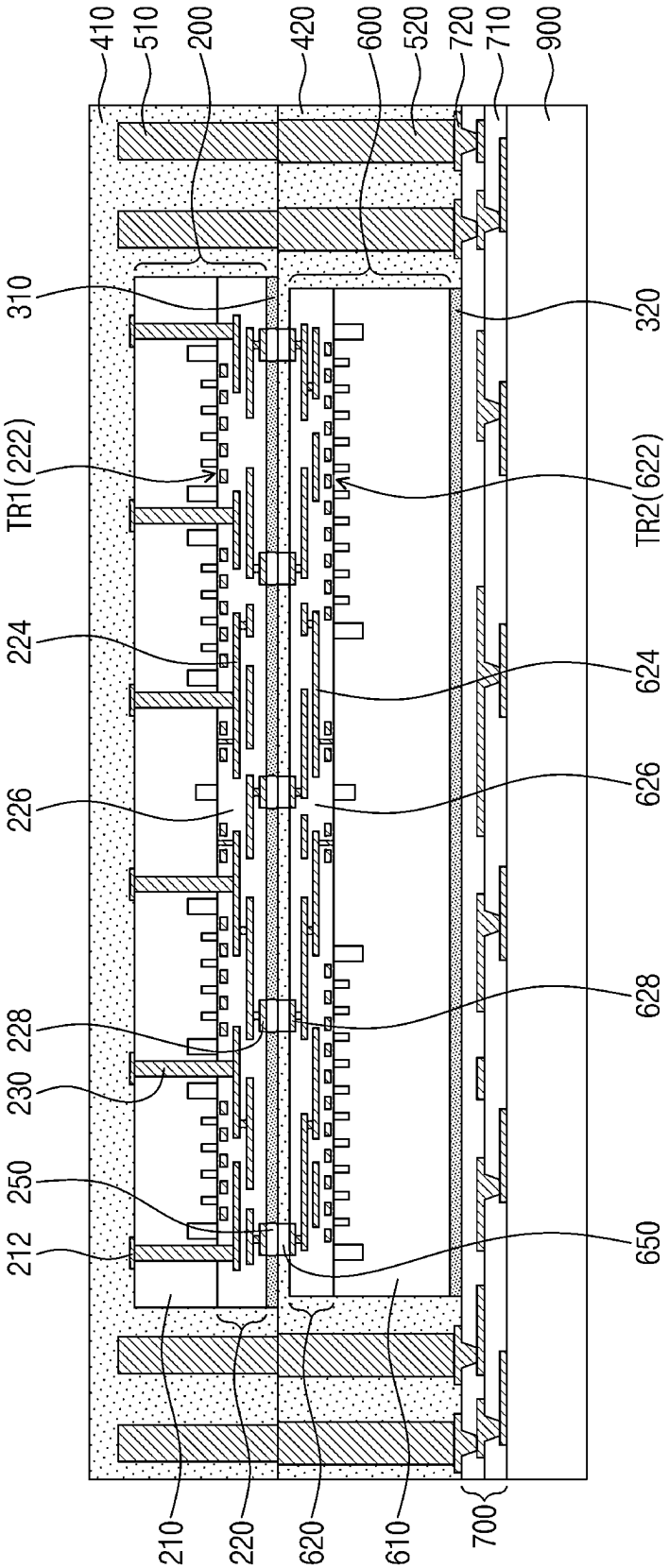
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FIG. 18

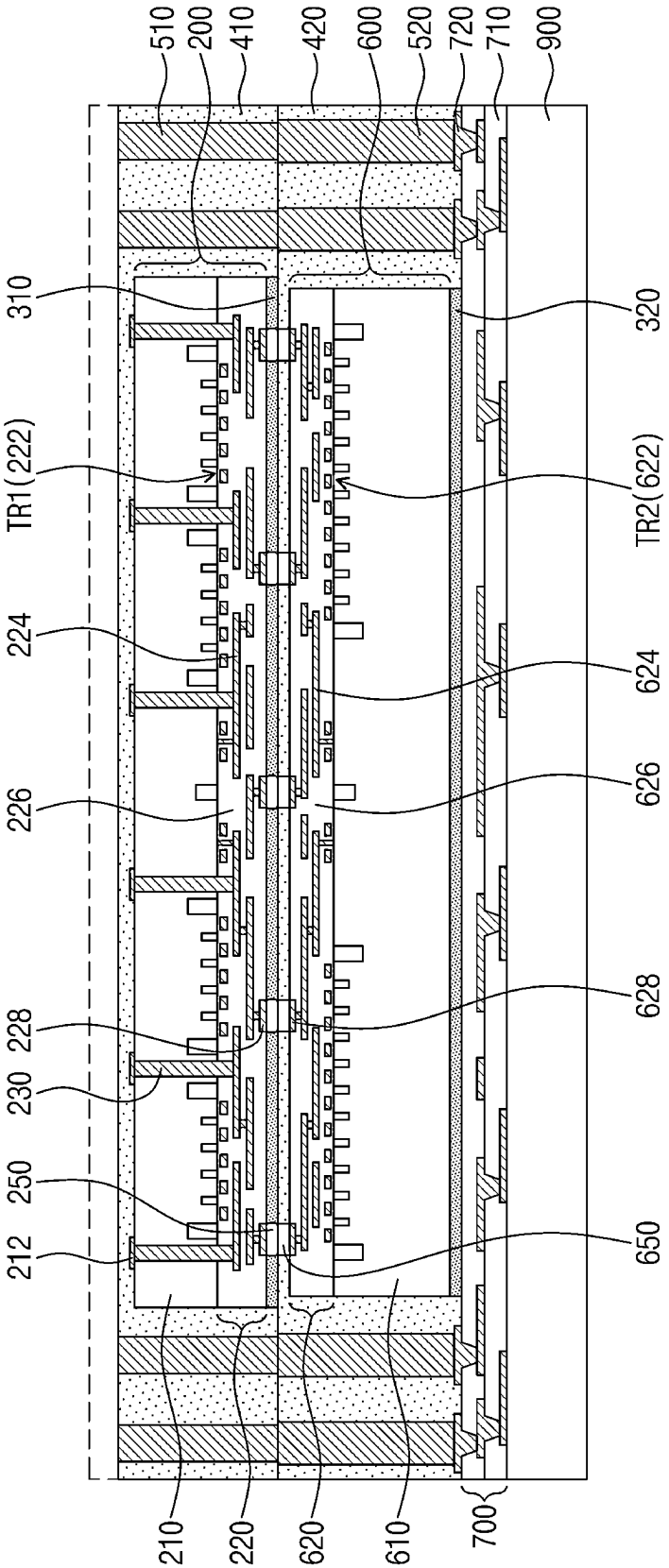
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FIG. 19

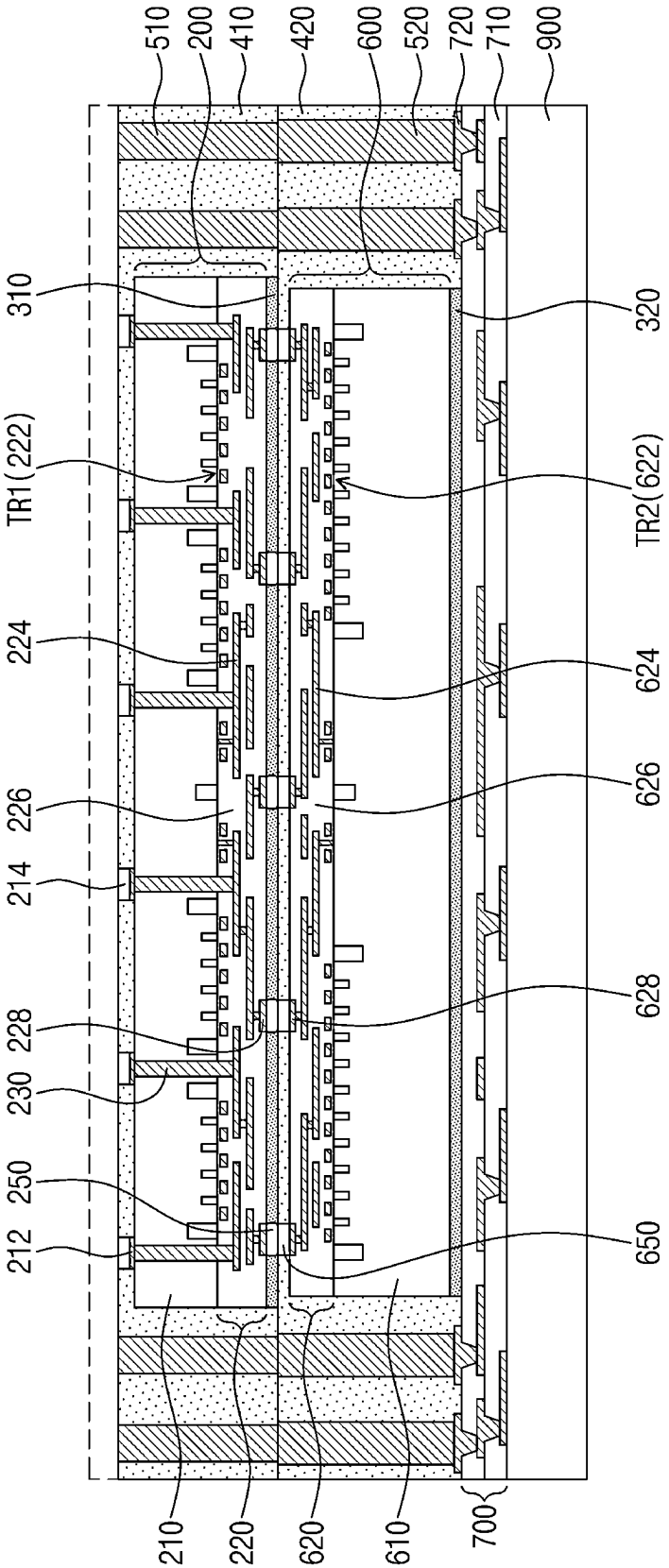
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FIG. 20

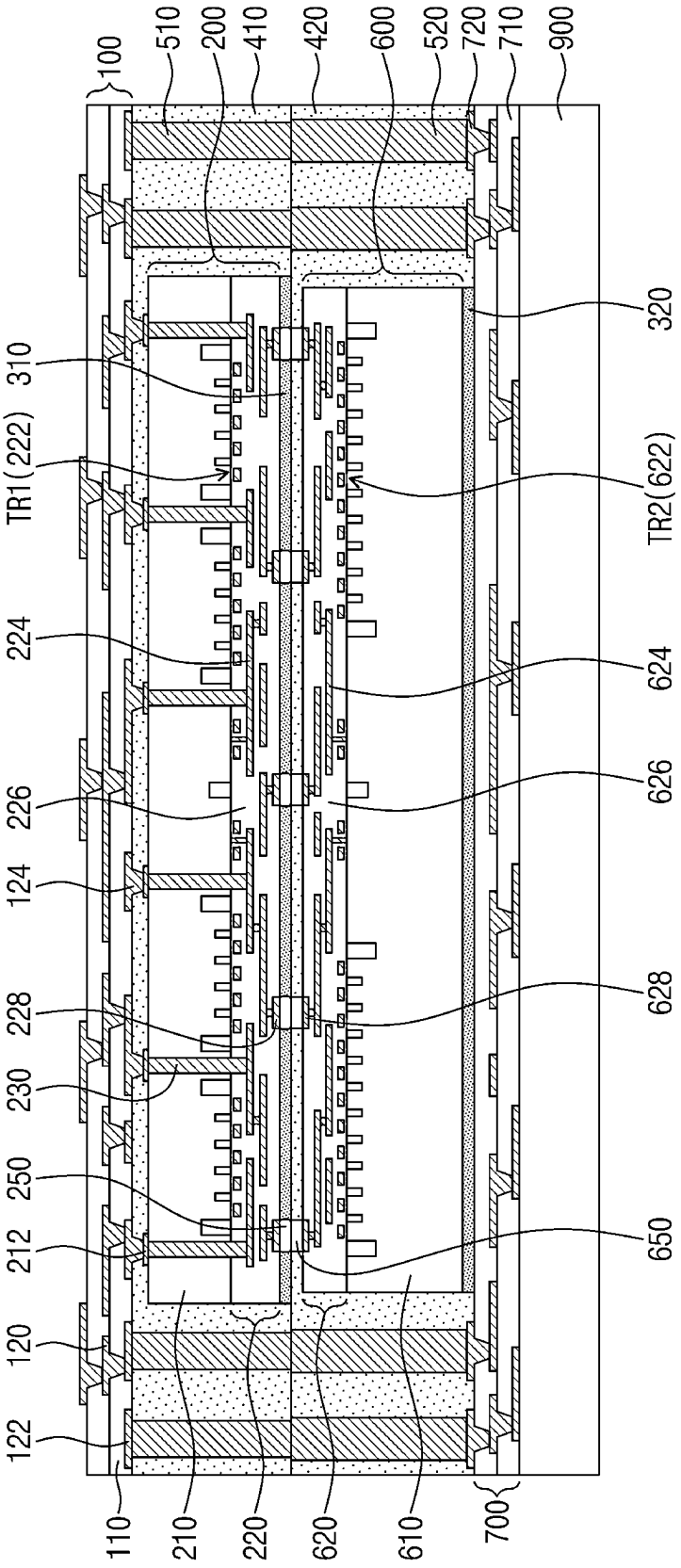
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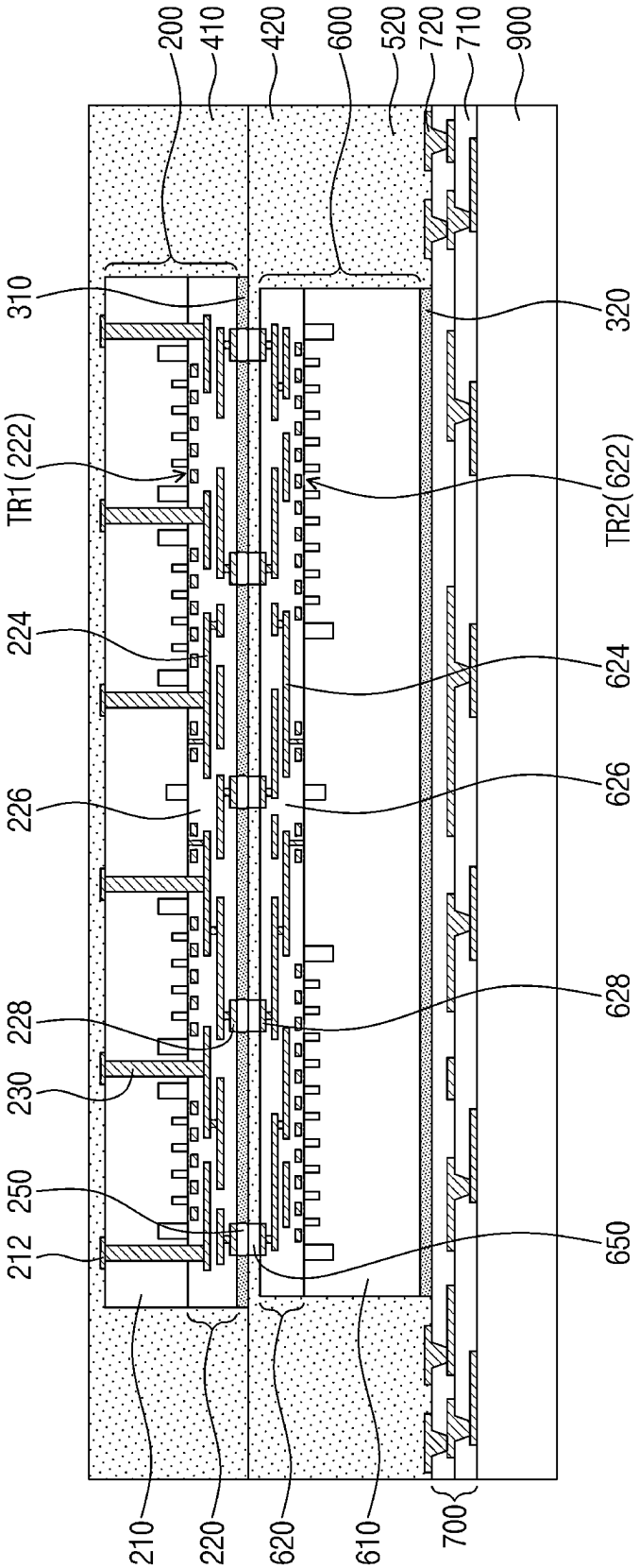
FIG. 21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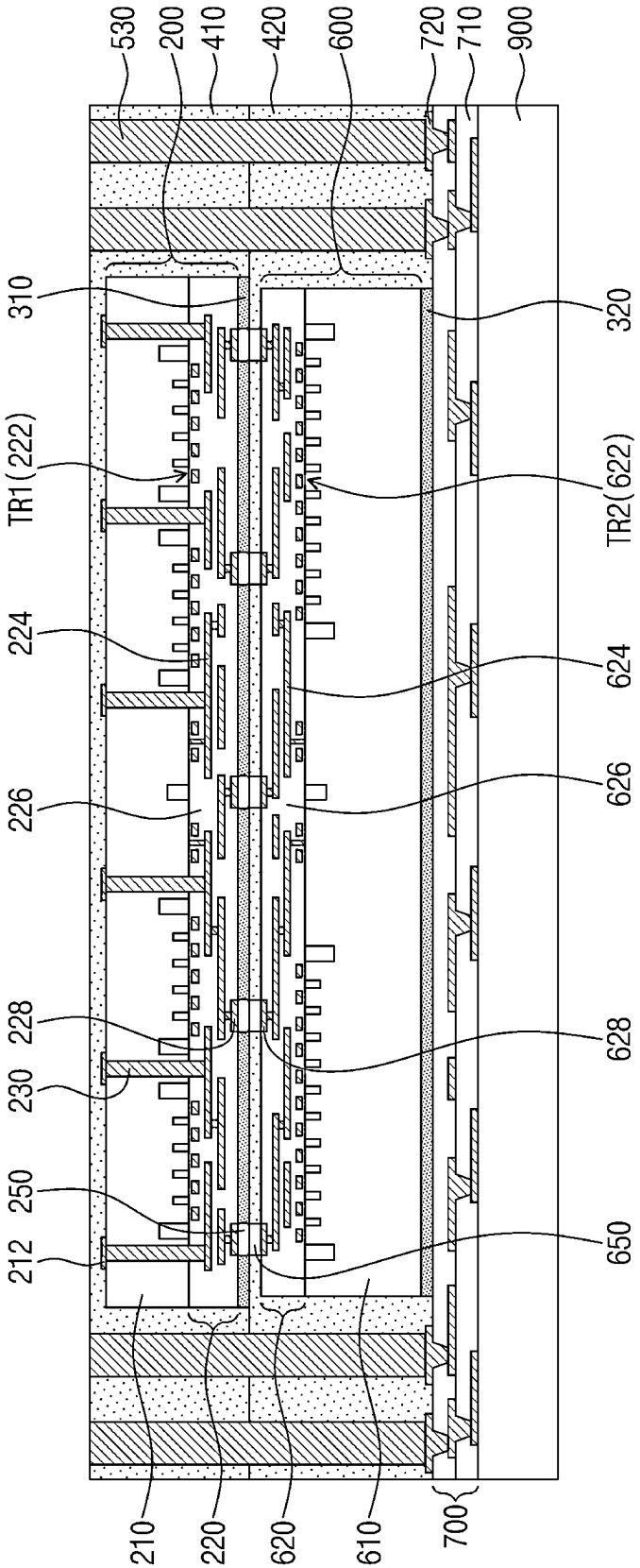
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FIG. 23

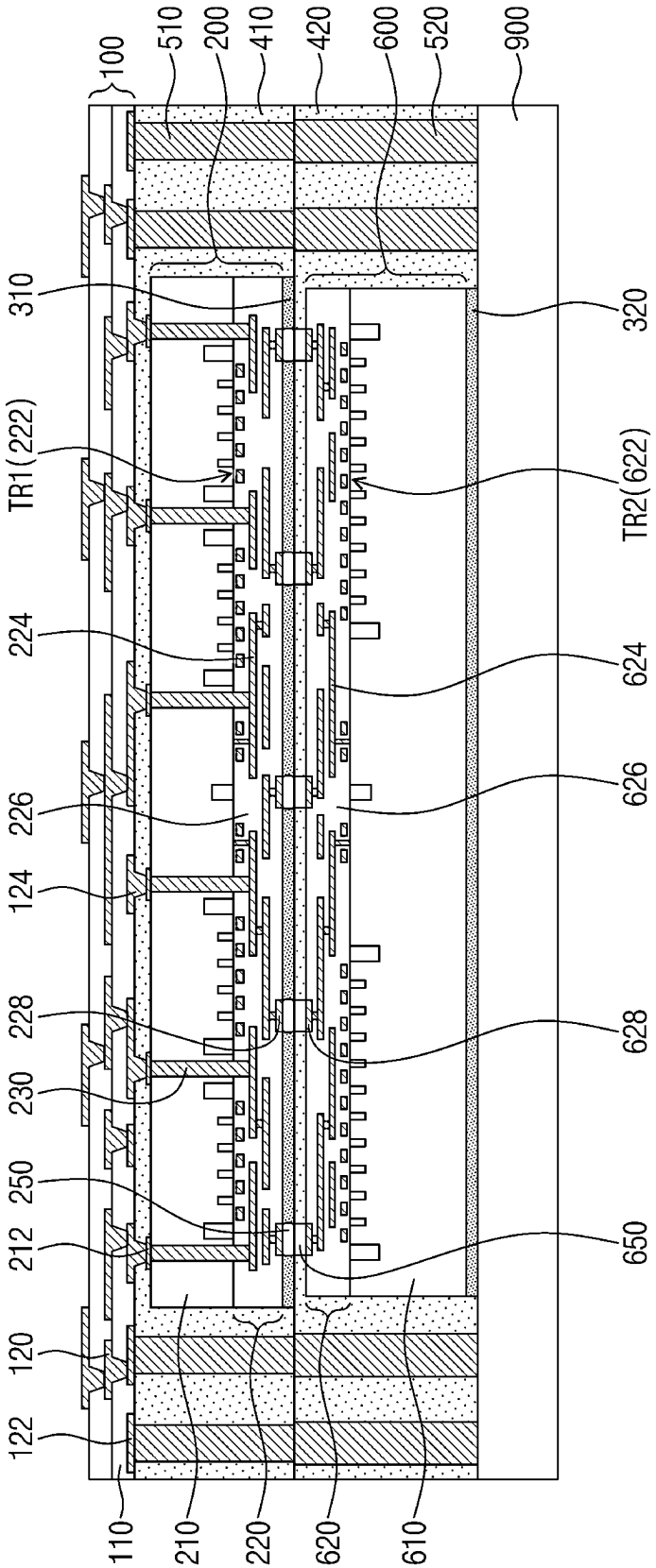
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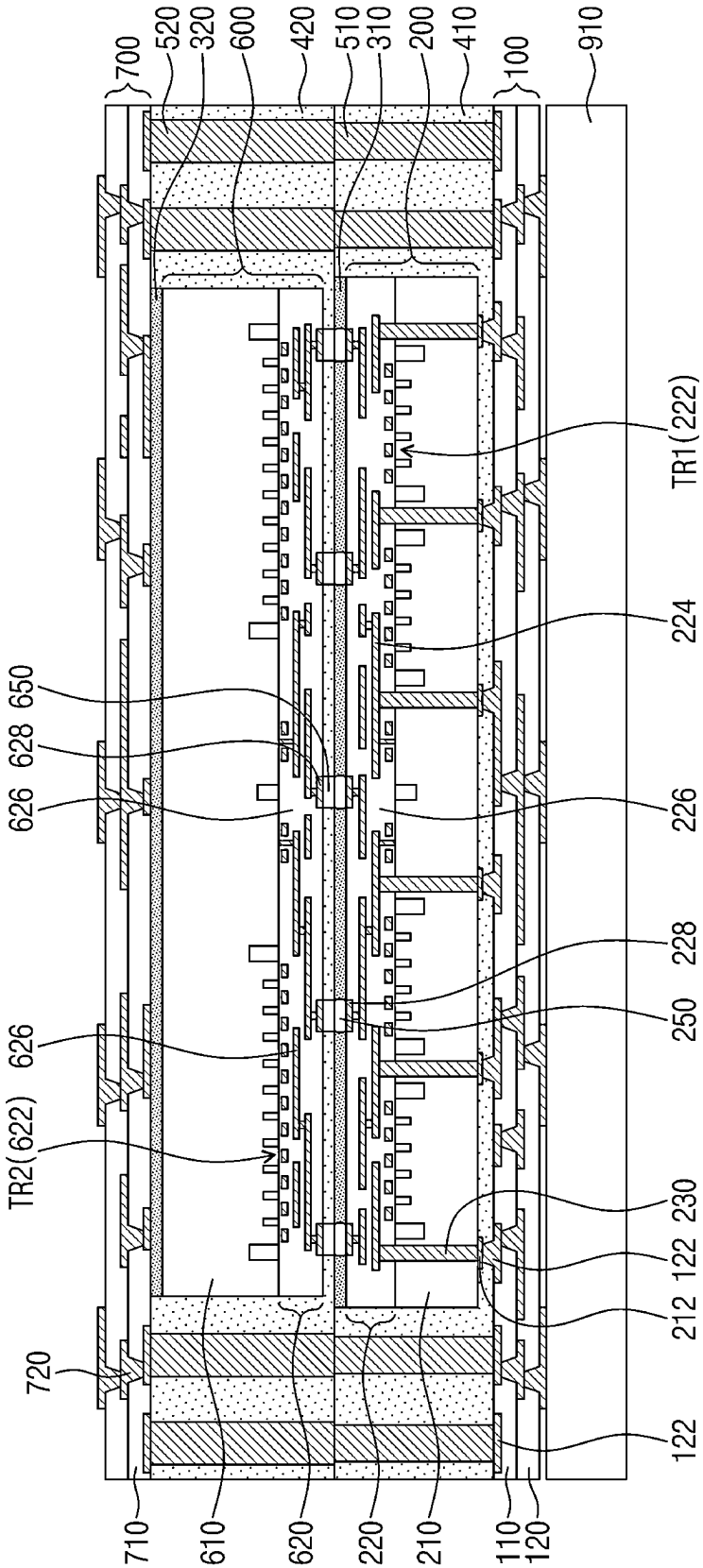
FIG. 24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SEMICONDUCTOR PACKAGE AND METHOD OF FABRICATING THE SAME

CROSS-REFERENCE TO RELATED APPLICATION

[0001] This U.S. non-provisional application claims priority under 35 U.S.C § 119 to Korean Patent Application No. 10-2024-0019769, filed on Feb. 8, 2024, in the Korean Intellectual Property Office, the disclosure of which is hereby incorporated by reference in its entirety.

BACKGROUND

1. Field

[0002] Embodiments of the present disclosure relate to a semiconductor package and a method of fabricating the same.

2. Brief Description of Related Art

[0003] With the development of the electronic industry, there have been increasing demands for electronic products to have high performance, high speed, and compact size. To meet the trend, there has recently been developed a packaging technology in which a plurality of semiconductor chips are mounted in a single package.

[0004] There has been an increasing demand for portable devices in recent electronic product markets, and as a result, it has been ceaselessly required for reduction in size and weight of electronic parts mounted on the portable devices. In order to accomplish the reduction in size and weight of the electronic parts, there is need for technology to integrate a number of individual devices into a single package as well as technology to reduce individual sizes of mounting parts. A large number of adhesive members are used to attach a plurality of devices to each other, and various problems occur due to an increase in the number of the adhesive members.

[0005] In the semiconductor industry, integrated circuit packaging technology has been developed to satisfy requirements for small-form-factor devices and high package reliability. For instance, package techniques capable of achieving a chip-size package are actively being developed to satisfy the requirements for small-form-factor devices, and package techniques capable of promoting efficiency in a package process and improving mechanical and electrical reliability of a packaged product have attracted considerable attention in terms of high package reliability.

SUMMARY

[0006] Some embodiments of the present disclosure provide a semiconductor package with improved structural stability and a method of fabricating the same.

[0007] Some embodiments of the present disclosure provide a simple and low-cost method of fabricating a semiconductor package and a semiconductor package fabricated by the same.

[0008] According to embodiments of the present disclosure, a semiconductor package is provided and includes: a first redistribution layer; a first semiconductor chip on the first redistribution layer; a first adhesive layer on a top surface of the first semiconductor chip; a first molding layer on the first redistribution layer, the first molding layer surrounding the first semiconductor chip and the first adhesive layer and extending between the first semiconductor chip and the first redistribution layer; a second semiconductor chip on the first adhesive layer; a second adhesive layer on a top surface of the second semiconductor chip; a second molding layer on the first molding layer, the second molding layer surrounding the second semiconductor chip and the second adhesive layer and extending between the second semiconductor chip and the first adhesive layer; and a second redistribution layer on the second molding layer, wherein the first semiconductor chip includes a first connection terminal that penetrates the first adhesive layer such that the first connection terminal is exposed at a top surface of the first adhesive layer, and wherein the second semiconductor chip includes a second connection terminal that penetrates the second molding layer such that the second connection terminal is coupled to the first connection terminal.

[0009] According to embodiments of the present disclosure, a semiconductor package is provided and includes: a first redistribution layer that includes a pad on a top surface of the first redistribution layer; a first semiconductor chip on the first redistribution layer, the first semiconductor chip including first connection terminals on a top surface of the first semiconductor chip; a first molding layer on the first redistribution layer, the first molding layer on the first semiconductor chip, and the first connection terminals is exposed at a top surface of the first molding layer; a first conductive post that penetrates the first molding layer and is coupled to the pad; a second semiconductor chip attached by a first adhesive layer to the top surface of the first molding layer; a second molding layer on the first molding layer, the second molding layer on the second semiconductor chip; a second conductive post that penetrates the second molding layer and is coupled to the first conductive post; a second redistribution layer on the second molding layer, the second redistribution layer including a wiring pattern that penetrates the second molding layer such that the wiring pattern is connected to the second semiconductor chip; and a plurality of external connection terminals on the second redistribution layer, wherein the first connection terminals are electrically connected to the second semiconductor chip.

[0010] According to embodiments of the present disclosure, a method of fabricating a semiconductor package is provided and includes: forming a first redistribution layer on a carrier substrate; forming, on the first redistribution layer, a first conductive post that vertically extends; attaching a first semiconductor chip by a first adhesive layer to a top surface of the first redistribution layer, the first semiconductor chip including first connection terminals on a top surface of the first semiconductor chip; forming, on the first redistribution layer, a first molding layer that is on the first conductive post and the first semiconductor chip; performing a grinding process to the first molding layer such that a top surface of the first conductive post and top surfaces of the first connection terminals become exposed; forming, on the first conductive post, a second conductive post that vertically extends; attaching, to the first molding layer, a second adhesive layer that is on the first connection terminals; attaching a second semiconductor chip to the second adhesive layer such that second connection terminals of the second semiconductor chip are inserted into the second adhesive layer and coupled to the first connection terminals; forming, on the first molding layer, a second molding layer that is on the second conductive post and the second

semiconductor chip; performing a grinding process to the second molding layer such that a top surface of the second conductive post is exposed; and forming a second redistribution layer on the second molding layer, wherein the second semiconductor chip includes a plurality of chip pads on an inactive surface of the second semiconductor chip, and the second connection terminals are on an active surface of the second semiconductor chip.

BRIEF DESCRIPTION OF DRAWINGS

[0011] FIG. **1** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0012] FIG. **2** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0013] FIG. **3** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0014] FIG. **4** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0015] FIG. **5** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0016] FIG. **6** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure . . .

[0017] FIGS. **7** to **24** illustrate cross-sectional views showing a method of fabricating a semiconductor package according to some embodiments of the present disclosure.

DETAILED DESCRIPTION

[0018] The following will now describe a semiconductor package according to non-limiting example embodiments of the present disclosure with reference to the accompanying drawings.

[0019] It will be understood that when an element or layer is referred to as being "on," "connected to," or "coupled to" another element or layer, it can be directly on, connected to, or coupled to the other element or layer or intervening elements or layers may be present. In contrast, when an element or layer is referred to as being "directly on," "directly connected to," or "directly coupled to" another element or layer, there are no intervening elements or layers present.

[0020] FIGS. **1** and **2** illustrate cross-sectional views showing a semiconductor package according to some embodiments of the present disclosure.

[0021] Referring to FIG. **1**, a first redistribution layer **100** may be provided. The first redistribution layer **100** may include one or more first substrate wiring layers that are stacked on each other. Each of the first substrate wiring layers may include a first redistribution dielectric layer **110** and a first redistribution conductive pattern **120** in the first redistribution dielectric layer **110**. When the first substrate wiring layer is provided in plural, the first redistribution conductive pattern **120** of one first substrate wiring layer may be electrically connected to the first redistribution conductive pattern **120** of an adjacent another first substrate wiring layer. In the following description, a single first substrate wiring layer will be used to explain the first redistribution dielectric layer **110** and the first redistribution conductive pattern **120**.

[0022] The first redistribution dielectric layer **110** may include a photo-imageable dielectric (PID). For example, the photo-imageable dielectric may include at least one from among photosensitive polyimide (PI), polybenzoxazole (PBO), phenolic polymers, and benzocyclobutene polymers. Alternatively, the first redistribution dielectric layer **110** may include a dielectric material. For example, the first redistribution dielectric layer **110** may include silicon oxide (SiO), silicon nitride (SiN), silicon oxynitride (SiON), silicon carbonitride (SiCN), or dielectric polymers.

[0023] The first redistribution conductive pattern **120** may be provided on the first redistribution dielectric layer **110**. The first redistribution conductive pattern **120** may horizontally extend on the first redistribution dielectric layer **110**. The first redistribution conductive pattern **120** may be a component for redistribution in the first redistribution layer **100**. The first redistribution conductive pattern **120** may include a conductive material. For example, the first redistribution conductive pattern **120** may include copper (Cu) or aluminum (Al).

[0024] The first redistribution conductive pattern **120** may have a damascene structure. For example, the first redistribution conductive pattern **120** may have a head portion and a tail portion that are integrally connected into a single unitary piece. The head and tail portions of the first redistribution conductive pattern **120** may have an inverse T-shaped cross section.

[0025] The head portion of the first redistribution conductive pattern **120** may be a pad or line part that allows a wiring line in the first redistribution layer **100** to horizontally expand. The head portion may be provided on a bottom surface of the first redistribution dielectric layer **110**. For example, the head portion may protrude onto the bottom surface of the first redistribution dielectric layer **110**. The first redistribution conductive pattern **120** of a lowermost one of the first substrate wiring layers may be exposed on a bottom surface of the first redistribution layer **100** or a bottom surface of a lowermost first redistribution dielectric layer **110**. The first redistribution conductive pattern **120** that is exposed may be substrate pads to which external terminals **130** are coupled. Alternatively, bumps or pads may be separately provided to allow the external terminals **130** to be coupled to the bottom surface of the first redistribution layer **100**, and the pads may be coupled to the first redistribution conductive pattern **120** that is exposed.

[0026] The tail portion of the first redistribution conductive pattern **120** may be a via part for vertical connection of a wiring line in the first redistribution layer **100**. The tail portion may be coupled to another first substrate wiring layer that overlaps with the tail portion. For example, the tail portion of the first redistribution conductive pattern **120** may extend from a top surface of the head portion, and may penetrate the first redistribution dielectric layer **110** to be coupled to the head portion of the first redistribution conductive pattern **120** included in another first substrate wiring layer that overlaps with the tail portion of the first redistribution conductive pattern **120**. No tail portion may be present in a portion **122** of the first redistribution conductive pattern **120** of an uppermost one of the first substrate wiring layers. The uppermost first redistribution conductive pattern (e.g, the portion **122**) having no tail portion may be pads of

the first redistribution layer **100** to which first conductive posts **510** are coupled as discussed below. Alternatively, the tail portion of another portion **124** of the uppermost first redistribution conductive pattern **120** may protrude onto a top surface of the first redistribution layer **100** or a top surface of the uppermost first redistribution dielectric layer **110**. The uppermost first redistribution conductive pattern **124** having the tail portion may be coupled to a first semiconductor chip **200** which will be discussed below.

[0027] The first redistribution layer **100** may be provided with external terminals **130** on the bottom surface thereof. The external terminals **130** may be coupled to the first redistribution conductive pattern **120** of the lowermost first substrate wiring layer. The external terminals **130** may include solder balls or solder bumps, and based on a type and arrangement of the external terminals **130**, a semiconductor package may be provided in the form of one from among a ball grid array (BGA) type, a fine ball-grid array (FBGA) type, and a land grid array (LGA) type.

[0028] A first semiconductor chip **200** may be disposed on the first redistribution layer **100**. The first semiconductor chip **200** may be disposed vertically spaced apart from the top surface of the first redistribution layer **100**. The first semiconductor chip **200** may include an integrated element therein. For example, the first semiconductor chip **200** may be a wafer-level die formed of a semiconductor, such as silicon (Si). The first semiconductor chip **200** may have a front surface and a rear surface. In the following description, the term "front surface" may be defined to indicate an active surface of an integrated element in a semiconductor chip, a surface on which wiring lines are formed, or a surface on which pads of a semiconductor chip are formed, and the term "rear surface" may be defined to indicate a surface opposite to the front surface. The rear surface of the first semiconductor chip **200** may be directed toward the first redistribution layer **100**. For example, the first semiconductor chip **200** may be face-up disposed on the first redistribution layer **100**.

[0029] The first semiconductor chip **200** may include a first semiconductor substrate **210**, a first circuit layer **220**, and vias **230**.

[0030] The first semiconductor substrate **210** may be provided. The first semiconductor substrate **210** may include a semiconductor material. For example, the first semiconductor substrate **210** may be a monocrystalline silicon (Si) substrate. The first semiconductor substrate **210** may have a top surface and a bottom surface that are opposite to each other. The top surface of the first semiconductor substrate **210** may be a front surface of the first semiconductor substrate **210**, and the bottom surface of the first semiconductor substrate **210** may be a rear surface of the first semiconductor substrate **210**. In this description, the front surface of the first semiconductor substrate **210** may be defined to indicate a surface on which semiconductor devices are formed or mounted in the first semiconductor substrate **210** or on which wiring lines and pads are formed in the first semiconductor substrate **210**, and the rear surface of the first semiconductor substrate **210** may be defined to indicate a surface opposite to the front surface. For example, the top surface of the first semiconductor substrate **210** may be an active surface.

[0031] The first semiconductor chip **200** may have the first circuit layer **220** provided on the top surface of the first semiconductor substrate **210**. The first circuit layer **220** may include a first semiconductor device **222** and a first device wiring part **224**.

[0032] The first semiconductor device **222** may include first transistors TR**1** provided on the top surface of the first semiconductor substrate **210**. For example, the first transistors TR**1** may each include a source and a drain that are formed on an upper portion of the first semiconductor substrate **210**, a gate electrode disposed on the top surface of the first semiconductor substrate **210**, and a gate dielectric layer interposed between the first semiconductor substrate **210** and the gate electrode. The first semiconductor device **222** may include a plurality of first transistors TR**1**. The first semiconductor device **222** may include a logic circuit or a memory circuit. According to embodiments, the first semiconductor device **222** may include a device isolation pattern, a logic cell, or a plurality of memory cells disposed on the top surface of the first semiconductor substrate **210**. Alternatively, the first semiconductor device **222** may include a passive element, such as a capacitor.

[0033] The top surface of the first semiconductor substrate **210** may be covered with a first device interlayer dielectric layer **226**. The first device interlayer dielectric layer **226** may bury the first semiconductor device **222**. For example, the first semiconductor device **222** may not be exposed by the first device interlayer dielectric layer **226**. The first device interlayer dielectric layer **226** may include, for example, at least one from among silicon oxide (SiO), silicon nitride (SiN), and silicon oxynitride (SiON). Alternatively, the first device interlayer dielectric layer **226** may include a low-k dielectric material. The first device interlayer dielectric layer **226** may have a mono-layered structure or a multi-layered structure. When the first device interlayer dielectric layer **226** is provided in the form of the multi-layered structure, an etch stop layer may be interposed between the dielectric layers. For example, the etch stop layer may be provided on top surfaces of the dielectric layers. The etch stop layer may include, for example, one from among silicon nitride (SiN), silicon oxynitride (SiON), and silicon carbonitride (SiCN).

[0034] The first device interlayer dielectric layer **226** may be provided therein with the first device wiring part **224** connected to the first transistors TR**1**. The first device wiring part **224** may include wiring patterns buried in the first device interlayer dielectric layer **226**. For example, the wiring patterns may include redistribution patterns for horizontal wiring and via patterns for vertical connection. The first device wiring part **224** may vertically penetrate the first device interlayer dielectric layer **226** to come into connection with one of a source electrode, a drain electrode, and a gate electrode of the first transistor TR**1**. Alternatively, the first device wiring part **224** may be connected to various components of the first semiconductor device **222**. The first device wiring part **224** may be positioned between top and bottom surfaces of the first device interlayer dielectric layer **226**. The first device wiring part **224** may include, for example, copper (Cu) or tungsten (W).

[0035] The first device interlayer dielectric layer **226** may be provided with first pads **228** on an upper portion thereof. The first pads **228** may have their top surfaces exposed at the top surface of the first device interlayer dielectric layer **226**. The top surfaces of the first pads **228** may be coplanar with the top surface of the first device interlayer dielectric layer **226**. The first pads **228** may be connected to the first device

wiring part **224**. The first pads **228** may include, for example, copper (Cu) or tungsten (W).

[0036] The first device interlayer dielectric layer **226** may be provided thereon with first connection terminals **250**. The first connection terminals **250** may be disposed on the top surfaces of the first pads **228**. The first connection terminals **250** may be coupled to the top surfaces of the first pads **228**. For example, the first connection terminals **250** may be bonding terminals that protrude onto the top surfaces of the first pads **228**. The first connection terminals **250** may include conductive bumps or solder balls. The first connection terminals **250** may include a metallic material. For example, the first connection terminals **250** may include copper (Cu).

[0037] Vias **230** may be provided to vertically penetrate the first semiconductor substrate **210** to come into connection with the first device wiring part **224**. The vias **230** may be patterns for vertical wiring. The vias **230** may vertically penetrate the first device interlayer dielectric layer **226** to be coupled to a bottom surface of a portion of the first device wiring part **224**. The vias **230** may vertically penetrate the first device interlayer dielectric layer **226** and the first semiconductor substrate **210** to be exposed at the bottom surface of the first semiconductor substrate **210**. The vias **230** may include, for example, tungsten (W).

[0038] The first semiconductor substrate **210** may be provided with backside pads **212** on the bottom surface thereof. The backside pads **212** may be connected to the vias **230**. The backside pads **212** may include, for example, copper (Cu) or tungsten (W).

[0039] The first semiconductor chip **200** may be mounted on the first redistribution layer **100**. The first semiconductor chip **200** may not be in contact with the top surface of the first redistribution layer **100**. The first semiconductor chip **200** may be vertically spaced apart from the top surface of the first redistribution layer **100**. In this case, the another portion **124** of the first redistribution conductive pattern **120** of the first redistribution layer **100** may extend from the first redistribution layer **100** toward the first semiconductor chip **200**, thereby being coupled to the backside pads **212**.

[0040] A first adhesive layer **310** may be disposed on the first semiconductor chip **200**. The first adhesive layer **310** may cover a top surface of the first circuit layer **220** of the first semiconductor chip **200**. The first adhesive layer **310** may surround the first connection terminals **250**. The first connection terminals **250** may have their top surfaces exposed at a top surface of the first adhesive layer **310**. The top surfaces of the first connection terminals **250** may be coplanar with the top surface of the first adhesive layer **310**. For example, the first connection terminals **250** may penetrate the first adhesive layer **310** to be coupled to the first pads **228**. The first adhesive layer **310** may have a width that is the same as the width of the first semiconductor chip **200**. In this case, a lateral surface of the first adhesive layer **310** may be aligned with a lateral surface of the first semiconductor chip **200**. Alternatively, as shown in FIG. **2**, the width of the first adhesive layer **310** may be greater than the width of the first semiconductor chip **200**. The first adhesive layer **310** may protrude past the lateral surface of the first semiconductor chip **200**. The first adhesive layer **310** may include a non-conductive film (NCF) or a non-conductive paste (NCP). The first adhesive layer **310** may include a dielectric polymer. For example, the first adhesive layer **310** may be formed of an epoxy-based material that contains no conductive particle. The use of the first adhesive layer **310** containing no conductive particle may achieve a fine pitch between the first connection terminals **250** without electrical short between neighboring first connection terminals **250**. In addition, as the first adhesive layer **310** serves as an underfill that fills a space between the first semiconductor chip **200** and a second molding layer **420**, which will be discussed below, or between the first semiconductor chip **200** and a second semiconductor chip **600**, which will be discussed below, the first connection terminals **250** may increase in mechanical durability.

[0041] A first molding layer **410** may be provided on the first redistribution layer **100**. On the first redistribution layer **100**, the first molding layer **410** may surround the first semiconductor chip **200** and the first adhesive layer **310**. The first adhesive layer **310** may be exposed at a top surface of the first molding layer **410**. The top surface of the first adhesive layer **310** may be coplanar with the top surface of the first molding layer **410**. The first molding layer **410** may fill a space between the first redistribution layer **100** and the first semiconductor chip **200**. The another portion **124** of the first redistribution conductive pattern **120** of the first redistribution layer **100** may be penetrate the first molding layer **410** positioned between the first redistribution layer **100** and the first semiconductor chip **200**, thereby being coupled to the backside pads **212**. The first molding layer **410** may include a dielectric material. For example, the first molding layer **410** may include a dielectric polymer material, such as an epoxy molding compound (EMC).

[0042] First conductive posts **510** may be provided on the first redistribution layer **100**. The first conductive posts **510** may serve as vertical connection terminals for connection between the first redistribution layer **100** and second conductive posts **520** which will be discussed below. The first conductive posts **510** may be horizontally spaced apart from the first semiconductor chip **200**. The first conductive posts **510** may each have a pillar shape. The first conductive posts **510** may vertically penetrate the first molding layer **410**. For example, the first conductive posts **510** may extend toward and be exposed at the top surface of the first molding layer **410**. The first conductive posts **510** may have their top surfaces coplanar with the top surface of the first molding layer **410** and the top surface of the first adhesive layer **310**. The first conductive posts **510** may extend toward a bottom surface of the first molding layer **410** to be coupled to the portion **122** (e.g., the pads) of the first redistribution conductive pattern **120**. The first conductive posts **510** may include a conductive material. For example, the first conductive posts **510** may include a metallic material, such as copper (Cu) or tungsten (W).

[0043] A second semiconductor chip **600** may be disposed on the first adhesive layer **310** and the first molding layer **410**. The second semiconductor chip **600** may include an integrated element therein. For example, the second semiconductor chip **600** may be a wafer-level die formed of a semiconductor, such as silicon (Si). The second semiconductor chip **600** may have a front surface and a rear surface. The front surface of the second semiconductor chip **600** may be directed towards the first redistribution layer **100**. For example, the second semiconductor chip **600** may be face-down disposed on the first molding layer **410**. The second semiconductor chip **600** may have a width less than the width of the first semiconductor chip **200**. An entirety of the second semiconductor chip **600** may vertically overlap a

portion of the first semiconductor chip **200**. Another portion of the first semiconductor chip **200** may vertically overlap with the first molding layer **410** positioned on one side of the second semiconductor chip **600**. However, embodiments of the present disclosure are not limited thereto, and the second semiconductor chip **600** may have a size the same as or greater than the size of the first semiconductor chip **200**. The second semiconductor chip **600** may be vertically spaced apart from the first adhesive layer **310** and the first molding layer **410**.

[0044] The second semiconductor chip **600** may include a second semiconductor substrate **610** and a second circuit layer **620**.

[0045] The second semiconductor substrate **610** may be provided. The second semiconductor substrate **610** may include a semiconductor material. For example, the second semiconductor substrate **610** may be a monocrystalline silicon (Si) substrate. The second semiconductor substrate **610** may have a top surface and a bottom surface that are opposite to each other. The bottom surface of the second semiconductor substrate **610** may be a front surface of the second semiconductor substrate **610**, and the top surface of the second semiconductor substrate **610** may be a rear surface of the second semiconductor substrate **610**. In this description, the front surface of the second semiconductor substrate **610** may be defined to indicate a surface on which semiconductor devices are formed or mounted in the second semiconductor substrate **610** or on which wiring lines and pads are formed in the second semiconductor substrate **610**, and the rear surface of the second semiconductor substrate **610** may be defined to indicate a surface opposite to the front surface. For example, the bottom surface of the second semiconductor substrate **610** may be an active surface.

[0046] The second semiconductor chip **600** may have the second circuit layer **620** provided on the bottom surface of the second semiconductor substrate **610**. The second circuit layer **620** may include a second semiconductor device **622** and a second device wiring part **624**.

[0047] The second semiconductor device **622** may include second transistors TR**2** provided on the bottom surface of the second semiconductor substrate **610**. For example, the second transistors TR**2** may each include a source and a drain that are formed on a lower portion of the second semiconductor substrate **610**, a gate electrode disposed on the bottom surface of the second semiconductor substrate **610**, and a gate dielectric layer interposed between the second semiconductor substrate **610** and the gate electrode. The second semiconductor device **622** may include a plurality of second transistors TR**2**. The second semiconductor device **622** may include a logic circuit or a memory circuit. According to embodiments, the second semiconductor device **622** may include a device isolation pattern, a logic cell, or a plurality of memory cells disposed on the bottom surface of the second semiconductor substrate **610**. Alternatively, the second semiconductor device **622** may include a passive element, such as a capacitor.

[0048] The bottom surface of the second semiconductor substrate **610** may be covered with a second device interlayer dielectric layer **626**. The second device interlayer dielectric layer **626** may bury the second semiconductor device **622**. For example, the second semiconductor device **622** may not be exposed by the second device interlayer dielectric layer **626**. The second device interlayer dielectric layer **626** may include, for example, at least one from among silicon oxide (SiO), silicon nitride (SiN), and silicon oxynitride (SiON). Alternatively, the second device interlayer dielectric layer **626** may have a low-k dielectric material. The second device interlayer dielectric layer **626** may have a mono-layered structure or a multi-layered structure. When the second device interlayer dielectric layer **626** is provided as the multi-layered structure, an etch stop layer may be interposed between the dielectric layers.

[0049] The second device interlayer dielectric layer **626** may be provided therein with the second device wiring part **624** connected to the second transistors TR**2**. The second device wiring part **624** may include wiring patterns buried in the second device interlayer dielectric layer **626**. For example, the wiring patterns may include redistribution patterns for horizontal wiring and via patterns for vertical connection. The second device wiring part **624** may vertically penetrate the second device interlayer dielectric layer **626** to come into connection with one from among a source electrode, a drain electrode, and a gate electrode of the second transistors TR**2**. Alternatively, the second device wiring part **624** may be connected to various components of the second semiconductor device **622**. The second device wiring part **624** may be positioned between top and bottom surfaces of the second device interlayer dielectric layer **626**. The second device wiring part **624** may include, for example, copper (Cu) or tungsten (W).

[0050] The second device interlayer dielectric layer **626** may be provided with second pads **628** on a lower portion thereof. The second pads **628** may have their bottom surfaces exposed at the bottom surface of the second device interlayer dielectric layer **626**. The bottom surfaces of the second pads **628** may be coplanar with the bottom surface of the second device interlayer dielectric layer **626**. The second pads **628** may be connected to the second device wiring part **624**. The second pads **628** may include, for example, copper (Cu) or tungsten (W).

[0051] The second device interlayer dielectric layer **626** may be provided with second connection terminals **650** on the bottom surface thereof. The second connection terminals **650** may be disposed on the bottom surfaces of the second pads **628**. The second connection terminals **650** may be coupled to the bottom surfaces of the second pads **628**. For example, the second connection terminals **650** may be bonding terminals that protrude onto the bottom surfaces of the second pads **628**. The second connection terminals **650** may include conductive bumps or solder balls. The second connection terminals **650** may include a metallic material. For example, the second connection terminals **650** may include copper (Cu).

[0052] The second semiconductor chip **600** may be mounted on the first semiconductor chip **200**. For example, the second semiconductor chip **600** may be disposed on the first adhesive layer **310**. The second circuit layer **620** of the second semiconductor chip **600** may be directed toward a top surface of the first semiconductor chip **200**. The second connection terminals **650** of the second semiconductor chip **600** may be vertically aligned with the first connection terminals **250** of the first semiconductor chip **200**. The first connection terminals **250** may be coupled to bottom surfaces of the second connection terminals **650**. For example, the second connection terminals **650** may serve as pads of the second semiconductor chip **600** such that the first connection terminals **250** are used to mount the first semiconductor chip **200**. An interface between the first connection terminals **250**

and the second connection terminals **650** may be coplanar with an interface between the first adhesive layer **310** and the second molding layer **420**.

[0053] A second adhesive layer **320** may be disposed on the second semiconductor chip **600**. The second adhesive layer **320** may cover a top surface of the second semiconductor substrate **610** of the second semiconductor chip **600**. The second adhesive layer **320** may have a width the same as a width of the second semiconductor chip **600**. In this case, a lateral surface of the second adhesive layer **320** may be aligned with a lateral surface of the second semiconductor chip **600**. Alternatively, the second adhesive layer **320** may protrude past the lateral surface of the second semiconductor chip **600**. The second adhesive layer **320** may include a die attach film (DAF).

[0054] The second molding layer **420** may be provided on the first molding layer **410**. On the first molding layer **410**, the second molding layer **420** may surround the second semiconductor chip **600** and the second adhesive layer **320**. The second adhesive layer **320** may be exposed at a top surface of the second molding layer **420**. A top surface of the second adhesive layer **320** may be coplanar with the top surface of the second molding layer **420**. The second molding layer **420** may fill a space between the first adhesive layer **310** and the second semiconductor chip **600** and a space between the first molding layer **410** and the second semiconductor chip **600**. The second connection terminals **650** may penetrate a portion of the second molding layer **420** positioned between the first molding layer **410** and the second semiconductor chip **600**, thereby being coupled to the first connection terminals **250**. The second molding layer **420** may include a dielectric material. For example, the second molding layer **420** may include a dielectric polymer material, such as an epoxy molding compound (EMC).

[0055] Second conductive posts **520** may be provided on the first molding layer **410**. The second conductive posts **520** may serve as vertical connection terminals for connecting the first conductive posts **510** to a second redistribution layer **700** which will be discussed below. The second conductive posts **520** may be horizontally spaced apart from the second semiconductor chip **600**. The second conductive posts **520** may each have a pillar shape. The second conductive posts **520** may vertically penetrate the second molding layer **420**. For example, the second conductive posts **520** may extend toward the top surface of the second molding layer **420**. The second conductive posts **520** may extend toward a bottom surface of the second molding layer **420** to be coupled to the first conductive posts **510**. A width of the second conductive posts **520** may be greater than a width of the first conductive posts **510**. The second conductive posts **520** may include a conductive material. For example, the second conductive posts **520** may include a metallic material, such as copper (Cu) or tungsten (W).

[0056] A second redistribution layer **700** may be provided on the second molding layer **420**. The second redistribution layer **700** may cover the top surface of the second molding layer **420** and the top surface of the second adhesive layer **320**. The second redistribution layer **700** may include one or more second substrate wiring layers that are stacked on each other. Each of the second substrate wiring layers may include a second redistribution dielectric layer **710** and a second redistribution conductive pattern **720** in the second redistribution dielectric layer **710**. When the second substrate wiring layer is provided in plural, the second redistribution conductive pattern **720** of one second substrate wiring layer may be electrically connected to the second redistribution conductive pattern **720** of adjacent another second substrate wiring layer. In the following description, a single second substrate wiring layer will be used to explain the second redistribution dielectric layer **710** and the second redistribution conductive pattern **720**.

[0057] The second redistribution dielectric layer **710** may include a photo-imageable dielectric (PID). For example, the photo-imageable dielectric may include at least one from among photosensitive polyimide (PI), polybenzoxazole (PBO), phenolic polymers, and benzocyclobutene polymers. Alternatively, the second redistribution dielectric layer **710** may include a dielectric material. For example, the second redistribution dielectric layer **710** may include silicon oxide (SiO), silicon nitride (SiN), silicon oxynitride (SiON), silicon carbonitride (SiCN), or dielectric polymers.

[0058] The second redistribution conductive pattern **720** may be provided on the second redistribution dielectric layer **710**. The second redistribution conductive pattern **720** may horizontally extend on the second redistribution dielectric layer **710**. The second redistribution conductive pattern **720** may be a component for redistribution in the second redistribution layer **700**. The second redistribution conductive pattern **720** may include a conductive material. For example, the second redistribution conductive pattern **720** may include copper (Cu) or aluminum (Al).

[0059] The second redistribution conductive pattern **720** may have a damascene structure. For example, the second redistribution conductive pattern **720** may have a head portion and a tail portion that are integrally connected into a single unitary piece. The head and tail portions of the second redistribution conductive pattern **720** may have an inverse T-shaped cross section.

[0060] The head portion of the second redistribution conductive pattern **720** may be a pad or line part that allows a wiring line in the second redistribution layer **700** to horizontally expand. The head portion may be provided on a bottom surface of the second redistribution dielectric layer **710**. For example, the head portion may protrude onto the bottom surface of the second redistribution dielectric layer **710**. The second redistribution conductive pattern **720** of a lowermost one of the second substrate wiring layers may be positioned on a bottom surface of a lowermost second redistribution dielectric layer **710** or a bottom surface of the second redistribution layer **700**. A lowermost second redistribution conductive pattern **720** may be pads to which the second conductive posts **520** are coupled. For example, the second conductive posts **520** may vertically penetrate the second molding layer **420** to be coupled to a bottom surface of the lowermost second redistribution conductive pattern **720**.

[0061] The tail portion of the second redistribution conductive pattern **720** may be a via part for vertical connection of a wiring line in the second redistribution layer **700**. The tail portion may be coupled to another second substrate wiring layer that overlaps the tail portion. For example, the tail portion of the second redistribution conductive pattern **720** may extend from a top surface of the head portion, and may penetrate the second redistribution dielectric layer **710** to be coupled to the head portion of the second redistribution conductive pattern **720** included in another second substrate wiring layer that overlaps with the tail portion of the second redistribution conductive pattern **720**. No tail portion may be

present in the second redistribution conductive pattern **720** of an uppermost one of the second substrate wiring layers. The uppermost second redistribution conductive pattern **720** may be exposed at a top surface of the second redistribution layer **700**, and may serve as pads for mounting another device or apparatus on a semiconductor package.

[0062] According to some embodiments of the present disclosure, the second semiconductor chip **600** may be bonded by the second adhesive layer **320** to the second redistribution layer **700**, and the first semiconductor chip **200** may be bonded by the first adhesive layer **310** to the second molding layer **420**. The first semiconductor chip **200** and the second semiconductor chip **600** may be rigidly adhered to other components in a semiconductor package, and the semiconductor package may improve in structural stability.

[0063] In the example embodiments that follow, a detailed description of technical features repetitive to those discussed above with reference to FIGS. **1** and **2** may be omitted, and a difference thereof will be discussed in detail. The same reference numerals may be allocated to the same components as those of the semiconductor package discussed above according to some embodiments of the present disclosure.

[0064] FIG. **3** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0065] Referring to FIG. **3**, third connection terminals **214** may be disposed on the bottom surface of the first semiconductor substrate **210**. The third connection terminals **214** may be placed on bottom surfaces of the backside pads **212**. The third connection terminals **214** may be coupled to the bottom surfaces of the backside pads **212**. For example, the third connection terminals **214** may be bonding terminals that protrude onto the bottom surfaces of the backside pads **212**. The third connection terminals **214** may have their bottom surfaces coplanar with a bottom surface of the first molding layer **410**. The third connection terminals **214** may include conductive bumps or solder balls. The third connection terminals **214** may include a metallic material. For example, the third connection terminals **214** may include copper (Cu).

[0066] The first semiconductor chip **200** may be mounted on the first redistribution layer **100**. The first semiconductor chip **200** may be mounted through the third connection terminals **214** on the first redistribution layer **100**. The third connection terminals **214** may be in contact with the top surface of the first redistribution layer **100**. For example, the another portion **124** of the first redistribution conductive pattern **120** may penetrate an uppermost first redistribution dielectric layer **110** to contact the third connection terminals **214**. The third connection terminals **214** may be coupled to the another portion **124** of the first redistribution conductive pattern **120** of the first redistribution layer **100**. The first semiconductor chip **200** may be vertically spaced apart from the first redistribution layer **100** across the third connection terminals **214**. Between the first redistribution layer **100** and the first semiconductor chip **200**, the first molding layer **410** may surround the third connection terminals **214** and the backside pads **212**.

[0067] The first conductive posts **510** may vertically penetrate the first molding layer **410** to contact the top surface of the first redistribution layer **100**. The portion **122** of the first redistribution conductive pattern **120** of the first redistribution layer **100** may penetrate the uppermost first redistribution dielectric layer **110** to be coupled to the first conductive posts **510**.

[0068] FIG. **4** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0069] Referring to FIG. **4**, first connection patterns **512** may be provided at the top surface of the first molding layer **410**. The first connection patterns **512** may have their top surfaces coplanar with the top surface of the first molding layer **410**. The first connection patterns **512** may be provided on the top surfaces of the first conductive posts **510**. The first conductive posts **510** may vertically penetrate the first molding layer **410** to connect the first connection patterns **512** to the first redistribution conductive pattern **120** of the first redistribution layer **100**. A width of the first connection patterns **512** may be greater than a width of the first conductive posts **510**. The second conductive posts **520** may vertically penetrate the second molding layer **420** to connect the first connection patterns **512** to the second redistribution conductive pattern **720**. The width of the first connection patterns **512** may be greater than a width of the second conductive posts **520**. For example, the first connection patterns **512** may be pads for connecting the first conductive posts **510** to the second conductive posts **520**.

[0070] Second connection patterns **652** may be provided at the top surface of the first adhesive layer **310**. The second connection patterns **652** may have their top surfaces coplanar with the top surface of the first adhesive layer **310**. The second connection patterns **652** may be provided on the first connection terminals **250**. The first connection terminals **250** may be coupled to bottom surfaces of the second connection patterns **652**. The first semiconductor chip **200** may be mounted through the first connection terminals **250** on the second connection patterns **652**. The second connection terminals **650** may be coupled to the top surfaces of the second connection patterns **652**. The second semiconductor chip **600** may be mounted through the second connection terminals **650** on the second connection patterns **652**. For example, the second connection patterns **652** may be pads for connecting the first connection terminals **250** of the first semiconductor chip **200** to the second connection terminals **650** of the second semiconductor chip **600**.

[0071] FIG. **5** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0072] Referring to FIG. **5**, a semiconductor package may include third conductive posts **530** in place of the first conductive posts **510** and the second conductive posts **520** discussed with reference to FIG. **1**.

[0073] The third conductive posts **530** may be vertical connection terminals for connecting the first redistribution layer **100** to the second redistribution layer **700**. The third conductive posts **530** may be horizontally spaced apart from the first semiconductor chip **200** and the second semiconductor chip **600**. The third conductive posts **530** may each have a pillar shape. The third conductive posts **530** may vertically penetrate the first molding layer **410** and the second molding layer **420**. For example, the third conductive posts **530** may extend toward the top surface of the second molding layer **420** to be coupled to the second redistribution conductive pattern **720** of the second redistribution layer **700**. The third conductive posts **530** may extend toward the bottom surface of the first molding layer **410** to be coupled

to the first redistribution conductive pattern **120** of the first redistribution layer **100**. The third conductive posts **530** may include a conductive material. For example, the third conductive posts **530** may include a metallic material, such as copper (Cu) or tungsten (W).

[0074] FIG. **6** illustrates a cross-sectional view showing a semiconductor package according to some embodiments of the present disclosure.

[0075] Referring to FIG. **6**, the second redistribution layer **700** may be provided on the second molding layer **420**. The second redistribution layer **700** may cover the top surface of the second molding layer **420** and the top surface of the second adhesive layer **320**. The second redistribution layer **700** may include one or more second substrate wiring layers that are stacked on each other. Each of the second substrate wiring layers may include a second redistribution dielectric layer **710** and a second redistribution conductive pattern **720** in the second redistribution dielectric layer **710**. When the second substrate wiring layer is provided in plural, the second redistribution conductive pattern **720** of one second substrate wiring layer may be electrically connected to the second redistribution conductive pattern **720** of adjacent another second substrate wiring layer. In the following description, a single second substrate wiring layer will be used to explain the second redistribution dielectric layer **710** and the second redistribution conductive pattern **720**.

[0076] The second redistribution dielectric layer **710** may include a photo-imageable dielectric (PID). Alternatively, the second redistribution dielectric layer **710** may include a dielectric material.

[0077] The second redistribution conductive pattern **720** may be provided on the second redistribution dielectric layer **710**. The second redistribution conductive pattern **720** may horizontally extend on the second redistribution dielectric layer **710**. The second redistribution conductive pattern **720** may be a component for redistribution in the second redistribution layer **700**. The second redistribution conductive pattern **720** may include a conductive material.

[0078] The second redistribution conductive pattern **720** may have a damascene structure. For example, the second redistribution conductive pattern **720** may have a head portion and a tail portion that are integrally connected into a single unitary piece. The head and tail portions of the second redistribution conductive pattern **720** may have a T-shaped cross section.

[0079] The head portion of the second redistribution conductive pattern **720** may be a pad or line part that allows a wiring line in the second redistribution layer **700** to horizontally expand. The head portion may be provided on a top surface of the second redistribution dielectric layer **710**. For example, the head portion may protrude onto the top surface of the second redistribution dielectric layer **710**. The second redistribution conductive pattern **720** of an uppermost one of second substrate wiring layers may be positioned on a top surface of an uppermost second redistribution dielectric layer **710** or the top surface of the second redistribution layer **700**. An uppermost second redistribution conductive pattern **720** may be pads through which an external apparatus or device is coupled to a semiconductor package.

[0080] The tail portion of the second redistribution conductive pattern **720** may be a via part for vertical connection of a wiring line in the second redistribution layer **700**. The tail portion may be coupled to another second substrate wiring layer that overlaps with the tail portion. For example, the tail portion of the second redistribution conductive pattern **720** may extend from a bottom surface of the head portion, and may penetrate the second redistribution dielectric layer **710** to be coupled to the head portion of the second redistribution conductive pattern **720** of adjacent another second substrate wiring layer that overlaps with the tail portion of the second redistribution conductive pattern **720**. No tail portion may be present in the second redistribution conductive pattern **720** of a lowermost one of the second substrate wiring layers. The lowermost second redistribution conductive pattern **720** may be exposed at a bottom surface of the second redistribution layer **700**, and may be pads to which the second conductive posts **520** are coupled. For example, the second conductive posts **520** may vertically penetrate the second molding layer **420** to be coupled to a bottom surface of the lowermost second redistribution conductive pattern **720**. A portion of the lowermost second redistribution conductive pattern **720** may be a wiring pattern for horizontal wiring.

[0081] FIGS. **7** to **20** illustrate cross-sectional views showing a method of fabricating a semiconductor package according to some embodiments of the present disclosure.

[0082] Referring to FIG. **7**, a first carrier substrate **900** may be provided. The first carrier substrate **900** may be a dielectric substrate including glass or polymer, or may be a conductive substrate including metal. The first carrier substrate **900** may be provided with an adhesive member on a top surface of the first carrier substrate **900**. For example, the adhesive member may include a glue tape.

[0083] A second redistribution layer **700** may be formed on the first carrier substrate **900**. For example, a metal layer may be formed on the first carrier substrate **900**, and the metal layer may be patterned to form substrate pads. A dielectric layer may be formed on the first carrier substrate **900** to cover the substrate pads, and the dielectric layer may be patterned to form openings that expose the substrate pads, with the result that a second redistribution dielectric layer **710** may be formed. A conductive layer may be formed to cover a top surface of the second redistribution dielectric layer **710** and to fill the openings, and the conductive layer may be patterned to form a second redistribution conductive pattern **720**. Therefore, a single second substrate wiring layer may be formed which includes the second redistribution dielectric layer **710** and the second redistribution conductive pattern **720**. The formation of the second substrate wiring layer may be repeatedly performed to form the second redistribution layer **700**.

[0084] Referring to FIG. **8**, second conductive posts **520** may be formed on the second redistribution layer **700**. For example, a sacrificial layer may be deposited on the second redistribution layer **700**, through holes may be formed to vertically penetrate the sacrificial layer to expose the second redistribution conductive pattern **720**, and then the through holes may be filled with a conductive material to form the second conductive posts **520**. Afterwards, the sacrificial layer may be removed.

[0085] Referring to FIG. **9**, a second semiconductor chip **600** may be provided. The second semiconductor chip **600** may be manufactured by an ordinary process. For example, a second semiconductor device **622** including second transistors TR**2** may be formed on one surface of the second semiconductor substrate **610**, a second circuit layer **620** may be formed on the one surface of the second semiconductor substrate **610** to include a second device wiring part **624**

connected to the second semiconductor device **622** and a second device interlayer dielectric layer **626** covering the second semiconductor device **622**, and then the second connection terminals **650** may be formed on second pads **628** of the second circuit layer **620**.

[0086] Thereafter, the second semiconductor chip **600** may be attached to a top surface of the second redistribution layer **700**. For example, a second adhesive layer **320** may be adhered to another surface of the second semiconductor substrate **610** of the second semiconductor chip **600**, and then the second adhesive layer **320** may be used to bond the second semiconductor chip **600** to the second redistribution layer **700**. The second adhesive layer **320** may include a die attach film (DAF). The second semiconductor chip **600** may be disposed between the second conductive posts **520**.

[0087] Referring to FIG. **10**, a second molding layer **420** may be formed on the second redistribution layer **700**. For example, a dielectric material may be coated on the second redistribution layer **700**, and then the dielectric material may be cured to form the second molding layer **420**. On the second redistribution layer **700**, the second molding layer **420** may cover the second semiconductor chip **600** and the second conductive posts **520**.

[0088] Referring to FIG. **11**, a portion of the second molding layer **420** may be removed. For example, a grinding process or a chemical mechanical polishing (CMP) process may be performed on a top surface of the second molding layer **420**. The grinding process or the chemical mechanical polishing process may continue until top surfaces of the second connection terminals **650** of the second semiconductor chip **600** are exposed and top surfaces of the second conductive posts **520** are exposed. The removed portions of the second molding layer **420** may be located at a level higher than a level of the top surfaces of the second connection terminals **650** and a level of the top surfaces of the second conductive posts **520**. The top surface of the second molding layer **420**, the top surfaces of the second connection terminals **650**, and the top surfaces of the second conductive posts **520** may be substantially flat and coplanar with each other.

[0089] Referring to FIG. **12**, first connection patterns **512** and second connection patterns **652** may be formed on the second molding layer **420**. For example, a conductive layer may be formed on the top surface of the second molding layer **420**, and then the conductive layer may be patterned to form the first connection patterns **512** and the second connection patterns **652**. The first connection patterns **512** may be connected to the top surfaces of the second conductive posts **520**. The second connection patterns **652** may be connected to the top surfaces of the second connection terminals **650**. In the embodiment of FIG. **12**, a semiconductor package may be fabricated which is discussed with reference to FIG. **4**. The first connection patterns **512** may not be manufactured as needed. The following description will focus on the embodiment of FIG. **11**.

[0090] Referring to FIG. **13**, on a resultant structure of FIG. **11**, first conductive posts **510** may be formed on the second molding layer **420**. For example, a sacrificial layer may be deposited on the second molding layer **420**, through holes may be formed to vertically penetrate the sacrificial layer to expose the second conductive posts **520**, and then the through holes may be filled with a conductive material to form the first conductive posts **510**. A width of the through holes may be less than a width of the second conductive posts **520**. Afterwards, the sacrificial layer may be removed.

[0091] Referring to FIG. **14**, a first adhesive layer **310** may be attached to the second molding layer **420**. The first adhesive layer **310** may cover the second connection terminals **650** exposed at the top surface of the second molding layer **420**. The first adhesive layer **310** may include a non-conductive film (NCF) or a non-conductive paste (NCP). When the first adhesive layer **310** is a non-conductive adhesive, the first adhesive layer **310** may be formed by dispensing a liquid non-conductive adhesive to coat the second molding layer **420**. When the first adhesive layer **310** is a non-conductive film, the first adhesive layer **310** may be formed by attaching a non-conductive film to the second molding layer **420**. The first adhesive layer **310** may be disposed between the first conductive posts **510**.

[0092] Referring to FIG. **15**, a first semiconductor chip **200** may be provided. The first semiconductor chip **200** may be manufactured by an ordinary process. For example, the first semiconductor chip **200** may be manufactured by forming, on one surface of a first semiconductor substrate **210**, a first semiconductor device **222** that includes first transistors TR**1**, forming on the one surface of the first semiconductor substrate **210** a first circuit layer **220** that includes a first device wiring part **224** connected to the first semiconductor device **222** and a first device interlayer dielectric layer **226** covering the first semiconductor device **222**, forming vias **230** that penetrate the first semiconductor substrate **210** to be connected to the first device wiring part **224** and exposed at another surface of the first semiconductor substrate **210**, forming on the another surface of the first semiconductor substrate **210** backside pads **212** that are connected to the vias **230**, and forming first connection terminals **250** on first pads **228** of the first circuit layer **220**. According to embodiments, on the another surface of the first semiconductor substrate **210**, third connection terminals **214** may be formed on the backside pads **212**.

[0093] According to some embodiments, the first adhesive layer **310** may be attached to the first semiconductor chip **200**. In this case, the first adhesive layer **310** may be attached to the first circuit layer **220** of the first semiconductor substrate **210** of the first semiconductor chip **200**. On the first circuit layer **220**, the first adhesive layer **310** may surround or cover the first connection terminals **250**. The following description will focus on the embodiment of FIG. **15**.

[0094] Referring to FIG. **16**, a thermocompression bonding process may be employed to mount the first semiconductor chip **200** on the second connection terminals **650**. The first connection terminals **250** and the second connection terminals **650** may electrically connect the first semiconductor chip **200** and the second semiconductor chip **600** to each other. For example, the first semiconductor chip **200** may be placed on the second molding layer **420** to allow the first connection terminals **250** to be aligned with the second connection terminals **650**, and then a bonding tool for a bonding process may be used to cause the first semiconductor chip **200** to approach the second molding layer **420**. In this step, the first connection terminals **250** may be inserted into the first adhesive layer **310**, and may be in contact with the second connection terminals **650**. Afterwards, the first connection terminals **250** may undergo a reflow process to bond the first connection terminals **250** to the second connection terminals **650**. After the thermocompression bond-

ing process, the first adhesive layer **310** may have the same width as a width of the first semiconductor chip **200**. In this case, a semiconductor package may be fabricated which is discussed with reference to FIG. **1**.

[0095] Alternatively, when the first semiconductor chip **200** is compressed in a direction toward the second molding layer **420**, the first adhesive layer **310** may protrude outwardly from a lateral surface of the first semiconductor chip **200**. Therefore, the first adhesive layer **310** may have a width greater than a width of the first semiconductor chip **200**. In this case, a semiconductor package may be fabricated which is discussed with reference to FIG. **2**. The following description will focus on the embodiment of FIG. **16**.

[0096] Referring to FIG. **17**, a first molding layer **410** may be formed on the second molding layer **420**. For example, a dielectric material may be coated on the second molding layer **420**, and then the dielectric material may be cured to form the first molding layer **410**. On the second molding layer **420**, the first molding layer **410** may cover the first semiconductor chip **200** and the first conductive posts **510**.

[0097] Referring to FIG. **18**, a portion of the first molding layer **410** may be removed. For example, a grinding process or a chemical mechanical polishing (CMP) process may be performed on a top surface of the first molding layer **410**. The grinding process or the chemical mechanical polishing process may continue until top surfaces of the first conductive posts **510** are exposed. The removed portion of the first molding layer **410** may be located at a level higher than a level of the top surfaces of the first conductive posts **510**. The top surface of the first molding layer **410** and the top surfaces of the first conductive posts **510** may be substantially flat and coplanar with each other. The first semiconductor chip **200** may be covered with the first molding layer **410**.

[0098] According to some embodiments, as shown in FIG. **19**, when the first semiconductor chip **200** includes third connection terminals **214** provided on the backside pads **212**, the grinding process or the chemical mechanical polishing process of the first molding layer **410** may continue until the top surfaces of the first conductive posts **510** and the third connection terminals **214** are exposed. Therefore, a removal action may be performed on a portion of the first molding layer **410** located at a level higher than a level of the top surfaces of the first conductive posts **510** and a level of top surfaces of the third connection terminals **214**. The top surface of the first molding layer **410**, the top surfaces of the third connection terminals **214**, and the top surfaces of the first conductive posts **510** may be substantially flat and coplanar with each other. The following description will focus on the embodiment of FIG. **18**.

[0099] Referring to FIG. **20**, a first redistribution layer **100** may be formed on the first molding layer **410**. For example, the first molding layer **410** may be patterned to form openings that expose the backside pads **212** of the first semiconductor chip **200**. A metal layer may be formed on the first molding layer **410** to cover the top surface of the first molding layer **410** and to fill the openings, and the metal layer may be patterned to form a first redistribution conductive pattern **120**. A dielectric layer may be formed on the first molding layer **410** to cover the first redistribution conductive pattern **120**, and the dielectric layer may be patterned to form openings that expose the first redistribution conductive pattern **120** to form a first redistribution dielectric layer **110**. A conductive layer may be formed to cover a top surface of the first redistribution dielectric layer **110** and to fill the openings, and the conductive layer may be patterned to form a first redistribution conductive pattern **120**. Therefore, a single first substrate wiring layer may be formed which includes the first redistribution dielectric layer **110** and the first redistribution conductive pattern **120**. The formation of the first substrate wiring layer may be repeatedly performed to form the first redistribution layer **100**.

[0100] Referring back to FIG. **1**, the first carrier substrate **900** (see FIG. **20**) may be removed. Then, external terminals **130** may be attached to the first redistribution layer **100**.

[0101] According to some embodiments of the present disclosure, the first semiconductor chip **200** and the second semiconductor chip **600** may be attached, stacked, and mounted on one first carrier substrate **900**, and in addition the first redistribution layer **100** and the second redistribution layer **700** may be formed on one first carrier substrate **900**. For example, a semiconductor package fabrication process may be continuously performed on one first carrier substrate **900**. Accordingly, the semiconductor package fabrication process may become simplified and decrease in manufacturing cost.

[0102] Moreover, the first semiconductor chip **200** and the second semiconductor chip **600** may be fixed by the first adhesive layer **310** and the second adhesive layer **320** in a semiconductor package, and a reflow process using solder balls or solder bumps may be used to bond the first semiconductor chip **200** and the second semiconductor chip **600** to each other. Thus, the bonding process of the first semiconductor chip **200** and the second semiconductor chip **600** may become simplified and decrease in manufacturing cost, and a semiconductor package with improved structural stability may be fabricated.

[0103] In the embodiments that follow, a detailed description of technical features repetitive to those discussed above with reference to FIGS. **7** to **20** may be omitted, and a difference thereof will be discussed in detail. The same reference numerals may be allocated to the same components as those of the semiconductor package discussed above according to some embodiments of the present disclosure.

[0104] FIGS. **21** and **22** illustrate cross-sectional views showing a method of fabricating a semiconductor package according to some embodiments of the present disclosure.

[0105] Referring to FIG. **21**, a second semiconductor chip **600** may be provided on a resultant structure of FIG. **7**. Thereafter, the second semiconductor chip **600** may be attached to a top surface of the second redistribution layer **700**. The bonding process of the second semiconductor chip **600** may be the same as or similar to the bonding process discussed with reference to FIG. **9**.

[0106] A second molding layer **420** may be formed on the second redistribution layer **700**. A portion of the second molding layer **420** may be removed. A grinding process or a chemical mechanical polishing (CMP) may continue until top surfaces of the second connection terminals **650** of the second semiconductor chip **600** are exposed. The formation of the second molding layer **420** and the partial removal of the second molding layer **420** may be similar to those discussed with reference to FIGS. **10** and **11**.

[0107] A first adhesive layer **310** may be used to bond a first semiconductor chip **200** to the second molding layer **420**. The first connection terminals **250** and the second

connection terminals **650** may electrically connect the first semiconductor chip **200** and the second semiconductor chip **600** to each other. The bonding process of the first semiconductor chip **200** may be the same as or similar to that discussed with reference to FIGS. **14** to **16**.

[0108] A first molding layer **410** may be formed on the second molding layer **420**. For example, a dielectric material may be coated on the second molding layer **420**, and then the dielectric material may be cured to form the first molding layer **410**. On the second molding layer **420**, the first molding layer **410** may cover the first semiconductor chip **200**.

[0109] Referring to FIG. **22**, third conductive posts **530** may be formed in the first molding layer **410** and the second molding layer **420**. For example, through holes may be formed to vertically penetrate the first molding layer **410** and the second molding layer **420** to expose the second redistribution conductive pattern **720**, and the through holes may be filled with a conductive material to form the third conductive posts **530**.

[0110] Referring back to FIG. **5**, a first redistribution layer **100** may be formed on the first molding layer **410**. The formation of the first redistribution layer **100** may be the same as or similar to that discussed with reference to FIG. **20**. The first carrier substrate **900** (see FIG. **20**) may be removed. Then, external terminals **130** may be attached to the first redistribution layer **100**.

[0111] FIGS. **23** and **24** illustrate cross-sectional views showing a method of fabricating a semiconductor package according to some embodiments of the present disclosure.

[0112] Referring to FIG. **23**, a first carrier substrate **900** may be provided.

[0113] Second conductive posts **520** may be formed on the first carrier substrate **900**. The formation of the second conductive posts **520** may be similar to that discussed with reference to FIG. **8**.

[0114] A second semiconductor chip **600** may be provided. Afterwards, the second semiconductor chip **600** may be attached to a top surface of the first carrier substrate **900**. The bonding process of the second semiconductor chip **600** may be similar to the bonding process discussed with reference to FIG. **9**.

[0115] A second molding layer **420** may be formed on the second redistribution layer **700**. A portion of the second molding layer **420** may be removed. A grinding process or a chemical mechanical polishing process may continue until top surfaces of the second connection terminals **650** of the second semiconductor chip **600** are exposed and top surfaces of the second conductive posts **520** are exposed. The formation of the second molding layer **420** and the partial removal of the second molding layer **420** may be similar to those discussed with reference to FIGS. **10** and **11**.

[0116] First conductive posts **510** may be formed on the second molding layer **420**. The formation of the first conductive posts **510** may be similar to that discussed with reference to FIG. **13**.

[0117] A first adhesive layer **310** may be used to bond a first semiconductor chip **200** to the second molding layer **420**. The first connection terminals **250** and the second connection terminals **650** may electrically connect the first semiconductor chip **200** and the second semiconductor chip **600** to each other. The bonding process of the first semiconductor chip **200** may be the same as or similar to the bonding process discussed with reference to FIGS. **14** to **16**.

[0118] A first molding layer **410** may be formed on the second molding layer **420**. A portion of the first molding layer **410** may be removed. A grinding process or a chemical mechanical polishing process may continue until top surfaces of the first conductive posts **510** are exposed. The formation of the first molding layer **410** and the partial removal of the first molding layer **410** may be similar to those discussed with reference to FIGS. **17** and **18**.

[0119] A first redistribution layer **100** may be formed on the first molding layer **410**. The formation of the first redistribution layer **100** may be similar to that discussed with reference to FIG. **20**.

[0120] Referring to FIG. **24**, a second carrier substrate **910** may be attached to the first redistribution layer **100**. The second carrier substrate **910** may be a dielectric substrate including glass or polymer, or may be a conductive substrate including metal. The second carrier substrate **910** may be attached through an adhesive member to the first redistribution layer **100**. For example, the adhesive member may include a glue tape.

[0121] A resultant structure may be turned over to cause the first carrier substrate **900** to reside above the second carrier substrate **910**.

[0122] After that, the first carrier substrate **900** may be removed. This step may expose a top surface of the second adhesive layer **320**, a top surface of the second molding layer **420**, and top surfaces of the second conductive posts **520**.

[0123] A second redistribution layer **700** may be formed on the second molding layer **420**. For example, a metal layer may be formed on the second molding layer **420** to cover the top surface of the second molding layer **420**, and the metal layer may be patterned to form a second redistribution conductive pattern **720**. A dielectric layer may be formed on the second molding layer **420** to cover the second redistribution conductive pattern **720**, and the dielectric layer may be patterned to form openings that expose the second redistribution conductive pattern **720** to form a second redistribution dielectric layer **710**. A conductive layer may be formed to cover a top surface of the second redistribution dielectric layer **710** and to fill the openings, and the conductive layer may be patterned to form a second redistribution conductive pattern **720**. Therefore, a single second substrate wiring layer may be formed which includes the second redistribution dielectric layer **710** and the second redistribution conductive pattern **720**. The formation of the second substrate wiring layer may be repeatedly performed to form the second redistribution layer **700**.

[0124] Referring back to FIG. **6**, the second carrier substrate **910** (see FIG. **24**) may be removed. Then, external terminals **130** may be attached to the first redistribution layer **100**.

[0125] In a semiconductor package according to some embodiments of the present disclosure, a second semiconductor chip may be attached through a second adhesive layer to a second redistribution layer, and a first semiconductor chip may be attached through a first adhesive layer to a second molding layer. For example, semiconductor chips may be rigidly adhered to other components in the semiconductor package, and the semiconductor package may improve in structural stability.

[0126] In a method of fabricating a semiconductor package according to some embodiments of the present disclosure, semiconductor chips may be attached, stacked, and

mounted on one carrier substrate, and redistribution layers may be formed on one carrier substrate. For example, a semiconductor package fabrication process may be continuously performed on one carrier substrate. Accordingly, the semiconductor package fabrication may become simplified and decrease in manufacturing cost.

[0127] Moreover, the semiconductor chips may be fixed through adhesive layers in the semiconductor package, and a reflow process may be used to bond the semiconductor chips to each other. Thus, the bonding process of the semiconductor chips may become simplified and decrease in manufacturing cost, and the semiconductor package may improve in structural stability.

[0128] Although non-limiting example embodiments of the present disclosure have been described in connection with the accompanying drawings, it will be understood by one of ordinary skill in the art that variations in form and detail may be made therein without departing from the spirit and scope of the present disclosure. The example embodiments described above should thus be considered illustrative and not restrictive.

What is claimed is:

1. A semiconductor package, comprising:
- a first redistribution layer;
- a first semiconductor chip on the first redistribution layer;
- a first adhesive layer on a top surface of the first semiconductor chip;
- a first molding layer on the first redistribution layer, the first molding layer surrounding the first semiconductor chip and the first adhesive layer and extending between the first semiconductor chip and the first redistribution layer;
- a second semiconductor chip on the first adhesive layer;
- a second adhesive layer on a top surface of the second semiconductor chip;
- a second molding layer on the first molding layer, the second molding layer surrounding the second semiconductor chip and the second adhesive layer and extending between the second semiconductor chip and the first adhesive layer; and
- a second redistribution layer on the second molding layer,
- wherein the first semiconductor chip comprises a first connection terminal that penetrates the first adhesive layer such that the first connection terminal is exposed at a top surface of the first adhesive layer, and
- wherein the second semiconductor chip comprises a second connection terminal that penetrates the second molding layer such that the second connection terminal is coupled to the first connection terminal.

2. The semiconductor package of claim **1**, wherein
- the first semiconductor chip is attached by the first adhesive layer to a bottom surface of the second molding layer, and
- the second semiconductor chip is attached by the second adhesive layer to a bottom surface of the second redistribution layer.

3. The semiconductor package of claim **1**, wherein the first semiconductor chip further comprises:
- a chip pad on a bottom surface of the first semiconductor chip; and
- a chip via that vertically penetrates the first semiconductor chip such that the chip via is connected to the chip pad,
- wherein the chip pad is electrically connected to the first redistribution layer.

4. The semiconductor package of claim **3**, wherein the first redistribution layer comprises:
- a dielectric pattern; and
- a wiring pattern in the dielectric pattern,
- wherein a portion of the wiring pattern penetrates the first molding layer such that the portion of the wiring pattern is connected to the chip pad.

5. The semiconductor package of claim **3**, wherein the first redistribution layer comprises:
- a dielectric pattern; and
- a wiring pattern in the dielectric pattern,
- wherein the first semiconductor chip further comprises a third connection terminal on the chip pad, the third connection terminal penetrating the first molding layer such that the third connection terminal is exposed at a bottom surface of the first molding layer, and
- wherein a portion of the wiring pattern penetrates the dielectric pattern such that the portion of the wiring pattern is connected to the third connection terminal.

6. The semiconductor package of claim **1**, further comprising:
- a first conductive post that vertically penetrates the first molding layer such that the first conductive post is connected to the first redistribution layer; and
- a second conductive post that vertically penetrates the second molding layer such that the second conductive post is connected to the first conductive post and the second redistribution layer, or
- a third conductive post that vertically penetrates the first molding layer and the second molding layer such that the third conductive post connects the first redistribution layer and the second redistribution layer to each other.

7. The semiconductor package of claim **1**, wherein
- the first semiconductor chip is vertically spaced apart from the first redistribution layer across the first molding layer, and
- the second semiconductor chip is vertically spaced apart from the first molding layer and the first adhesive layer across the second molding layer.

8. The semiconductor package of claim **1**, wherein
- the top surface of the first adhesive layer is coplanar with a top surface of the first molding layer, and
- a top surface of the second adhesive layer is coplanar with a top surface of the second molding layer.

9. The semiconductor package of claim **1**, further comprising a plurality of external connection terminals on a bottom surface of the first redistribution layer.

10. The semiconductor package of claim **1**, wherein an interface between the first connection terminal and the second connection terminal is coplanar with an interface between the first adhesive layer and the second molding layer.

11. The semiconductor package of claim **1**, wherein a width of the second adhesive layer is the same as or greater than a width of the first semiconductor chip.

12. A semiconductor package, comprising:
- a first redistribution layer that comprises a pad on a top surface of the first redistribution layer;
- a first semiconductor chip on the first redistribution layer, the first semiconductor chip comprising first connection terminals on a top surface of the first semiconductor chip;

a first molding layer on the first redistribution layer, the first molding layer on the first semiconductor chip, and the first connection terminals is exposed at a top surface of the first molding layer;

a first conductive post that penetrates the first molding layer and is coupled to the pad;

a second semiconductor chip attached by a first adhesive layer to the top surface of the first molding layer;

a second molding layer on the first molding layer, the second molding layer on the second semiconductor chip;

a second conductive post that penetrates the second molding layer and is coupled to the first conductive post;

a second redistribution layer on the second molding layer, the second redistribution layer comprising a wiring pattern that penetrates the second molding layer such that the wiring pattern is connected to the second semiconductor chip; and

a plurality of external connection terminals on the second redistribution layer,

wherein the first connection terminals are electrically connected to the second semiconductor chip.

13. The semiconductor package of claim **12**, wherein the first semiconductor chip is attached by a second adhesive layer to the top surface of the first redistribution layer.

14. The semiconductor package of claim **12**, wherein the second semiconductor chip comprises a plurality of second connection terminals on a bottom surface of the second semiconductor chip, and

wherein the second connection terminals penetrate the first adhesive layer such that the second connection terminals are connected to the first connection terminals.

15. The semiconductor package of claim **12**, wherein the second semiconductor chip comprises:

a chip pad on a top surface of the second semiconductor chip; and

a chip via that vertically penetrates the second semiconductor chip such that the chip via is connected to the chip pad,

wherein the wiring pattern is coupled to the chip pad.

16. The semiconductor package of claim **12**, wherein

the first molding layer is on the top surface of the first semiconductor chip, and

the first molding layer vertically separates the top surface of the first semiconductor chip from the first adhesive layer or the second molding layer.

17. The semiconductor package of claim **12**, wherein a width of the first adhesive layer is the same as or greater than a width of the second semiconductor chip.

18. The semiconductor package of claim **12**, wherein a width of the second conductive post is less than a width of the first conductive post.

19. The semiconductor package of claim **12**, wherein an active surface of the first semiconductor chip faces an active surface of the second semiconductor chip.

20. A method of fabricating a semiconductor package, the method comprising:

forming a first redistribution layer on a carrier substrate;

forming, on the first redistribution layer, a first conductive post that vertically extends;

attaching a first semiconductor chip by a first adhesive layer to a top surface of the first redistribution layer, the first semiconductor chip including first connection terminals on a top surface of the first semiconductor chip;

forming, on the first redistribution layer, a first molding layer that is on the first conductive post and the first semiconductor chip;

performing a grinding process to the first molding layer such that a top surface of the first conductive post and top surfaces of the first connection terminals become exposed;

forming, on the first conductive post, a second conductive post that vertically extends;

attaching, to the first molding layer, a second adhesive layer that is on the first connection terminals;

attaching a second semiconductor chip to the second adhesive layer such that second connection terminals of the second semiconductor chip are inserted into the second adhesive layer and coupled to the first connection terminals;

forming, on the first molding layer, a second molding layer that is on the second conductive post and the second semiconductor chip;

performing a grinding process to the second molding layer such that a top surface of the second conductive post is exposed; and

forming a second redistribution layer on the second molding layer,

wherein the second semiconductor chip includes a plurality of chip pads on an inactive surface of the second semiconductor chip, and the second connection terminals are on an active surface of the second semiconductor chip.

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